

FIG. 1

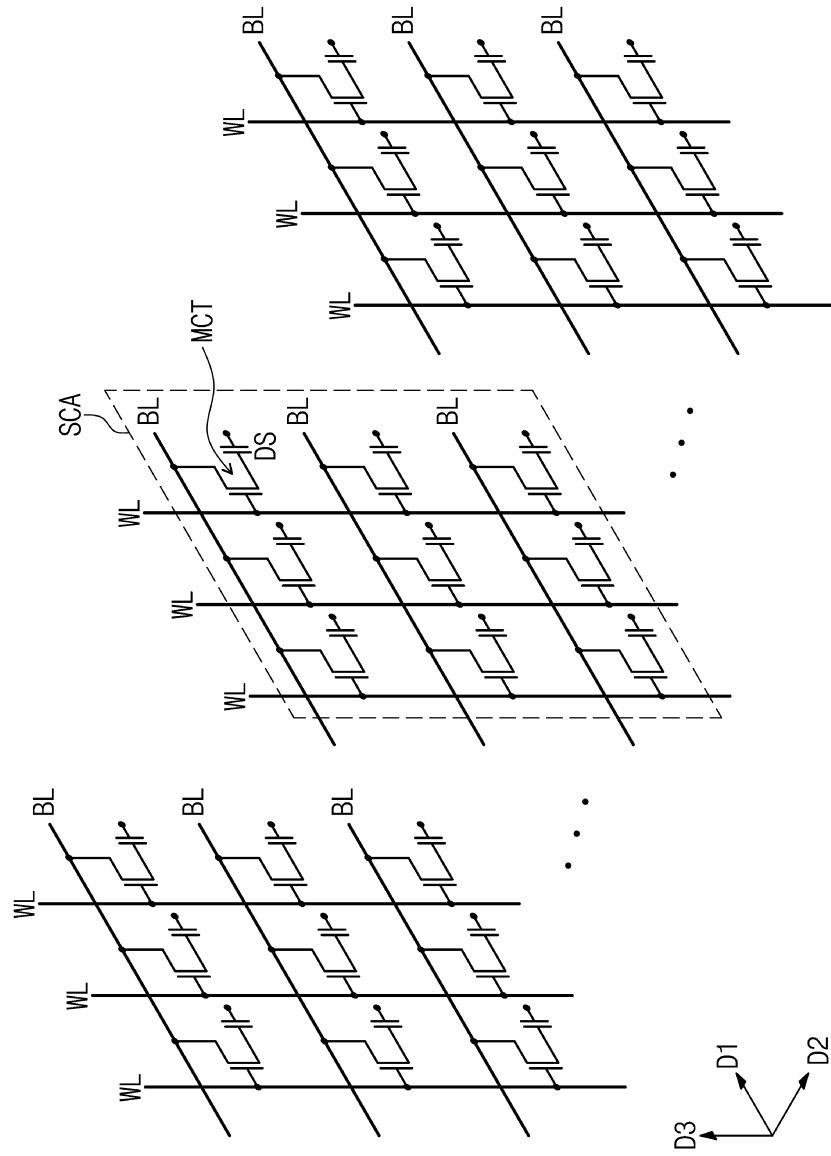


FIG. 2

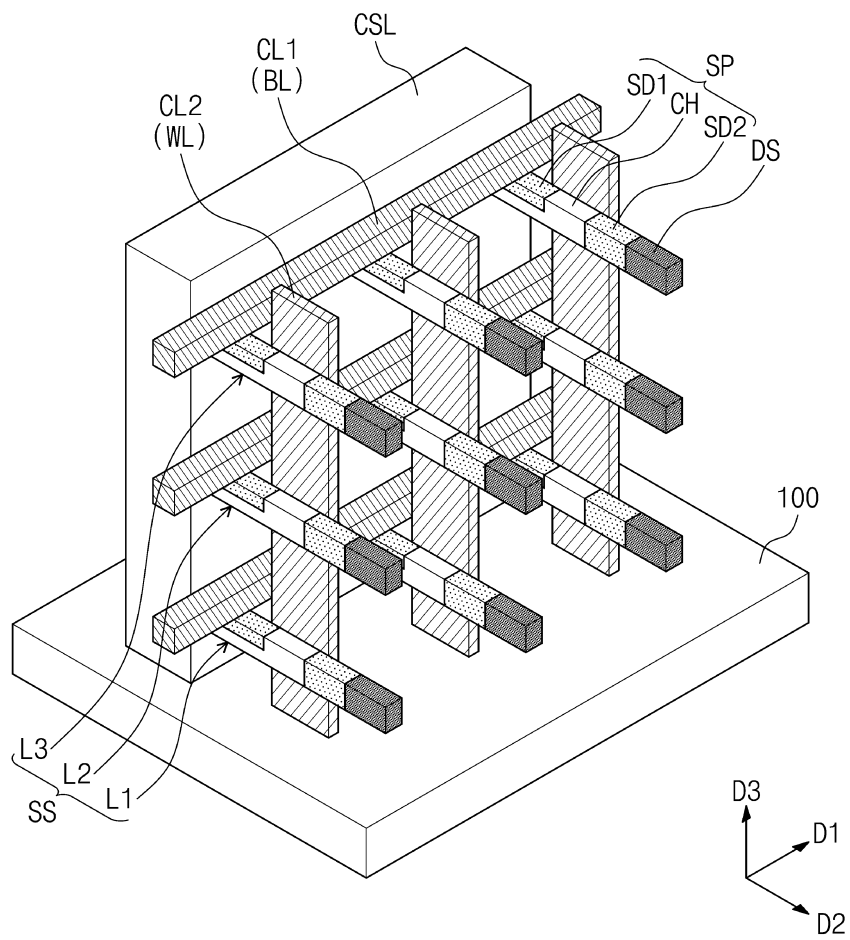


FIG. 3

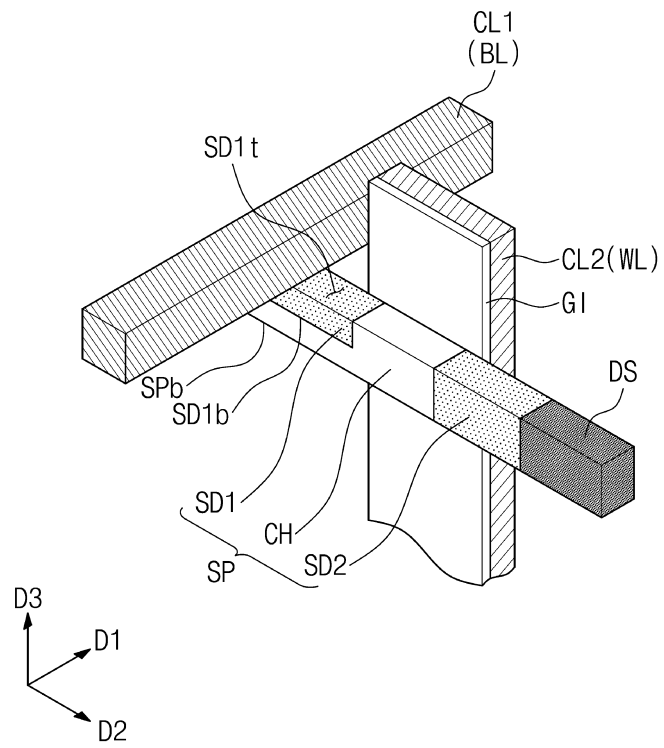


FIG. 4A

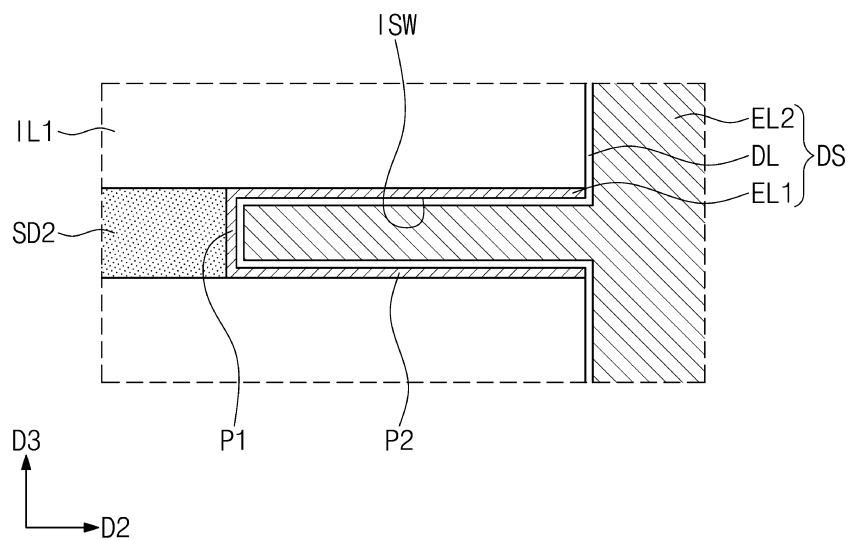


FIG. 4B

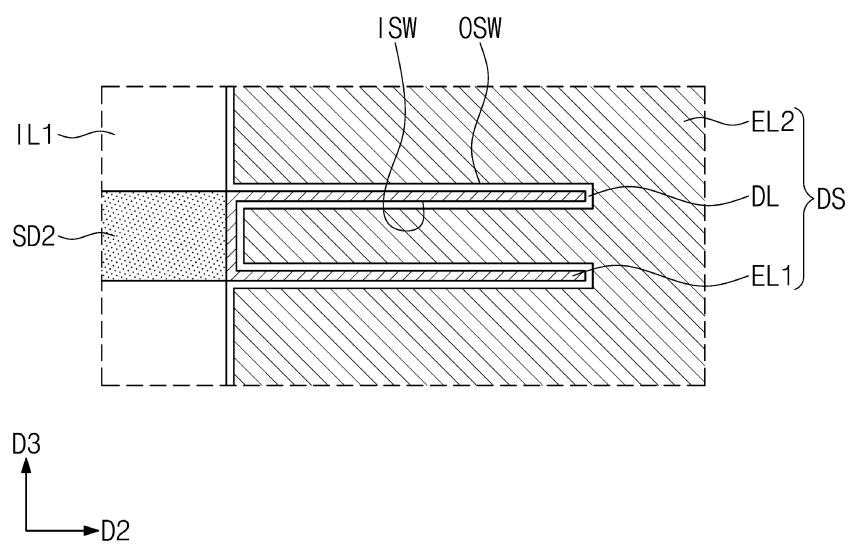


FIG. 4C

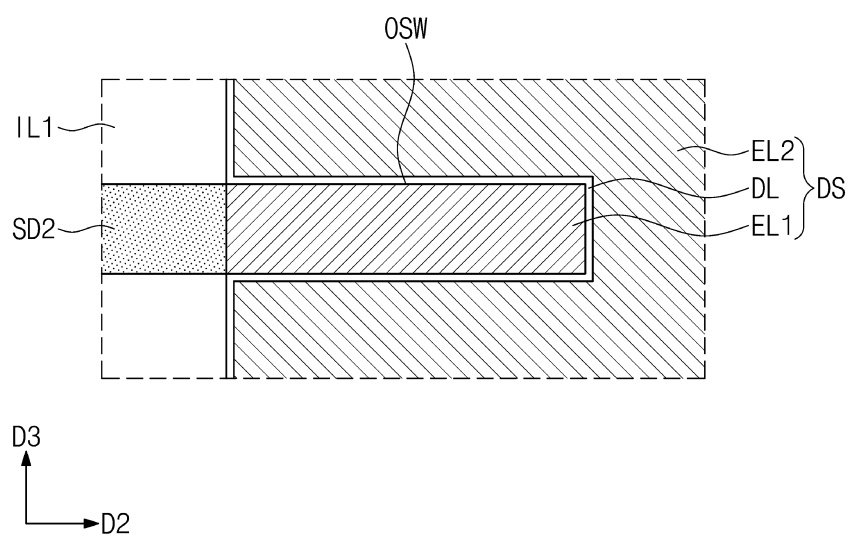


FIG. 5

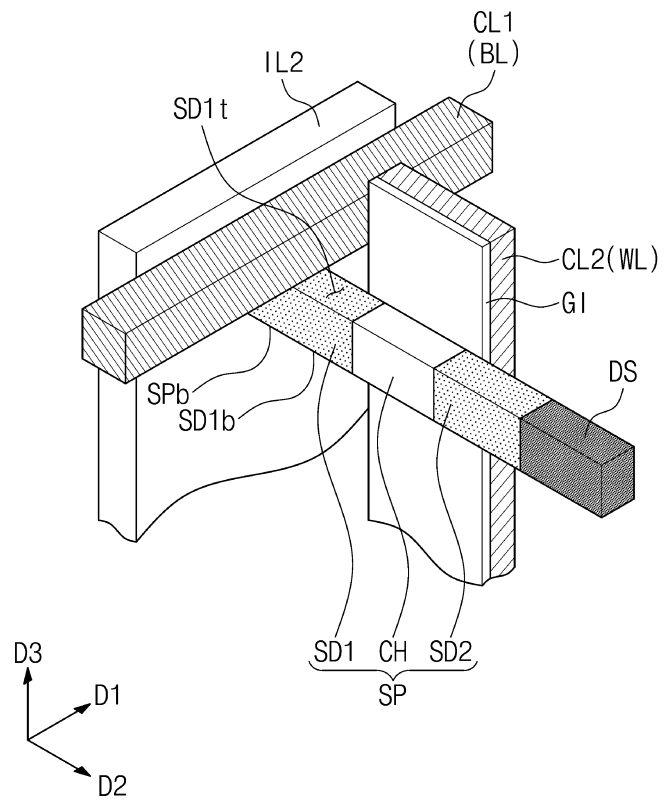


FIG. 6

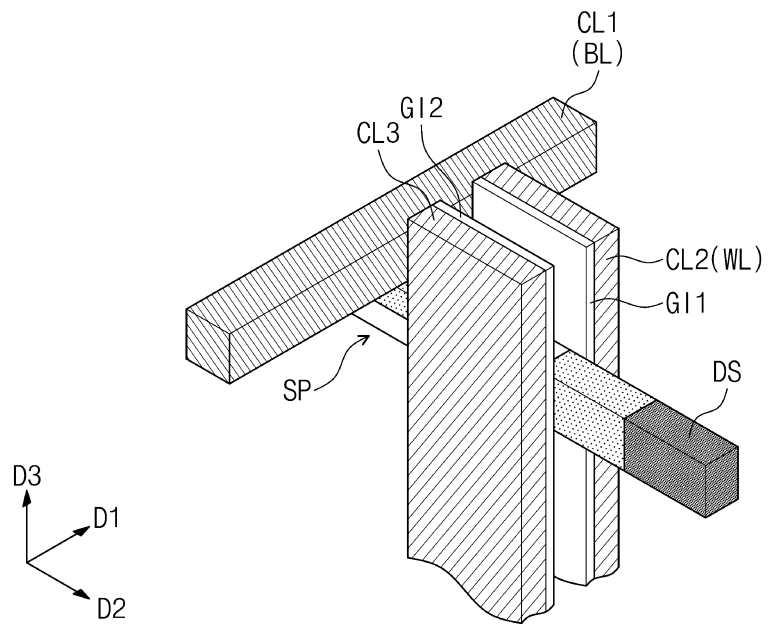


FIG. 7

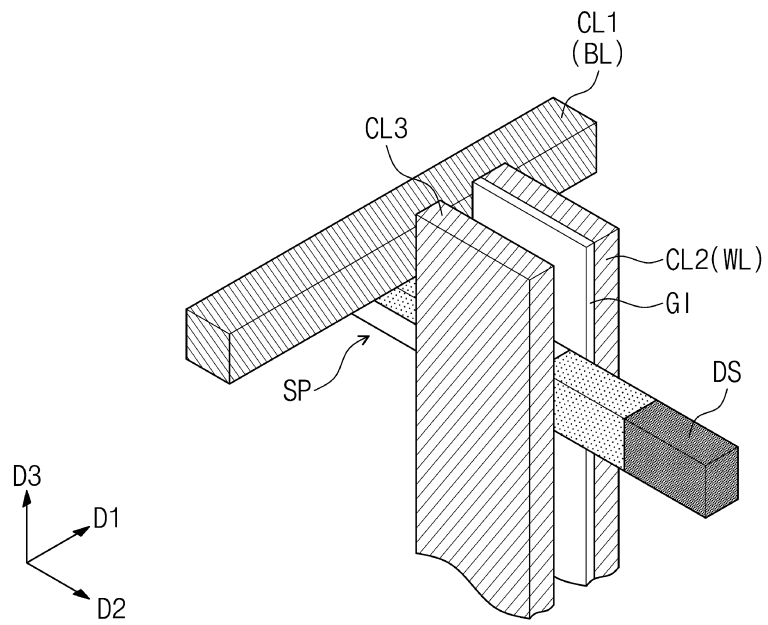


FIG. 8

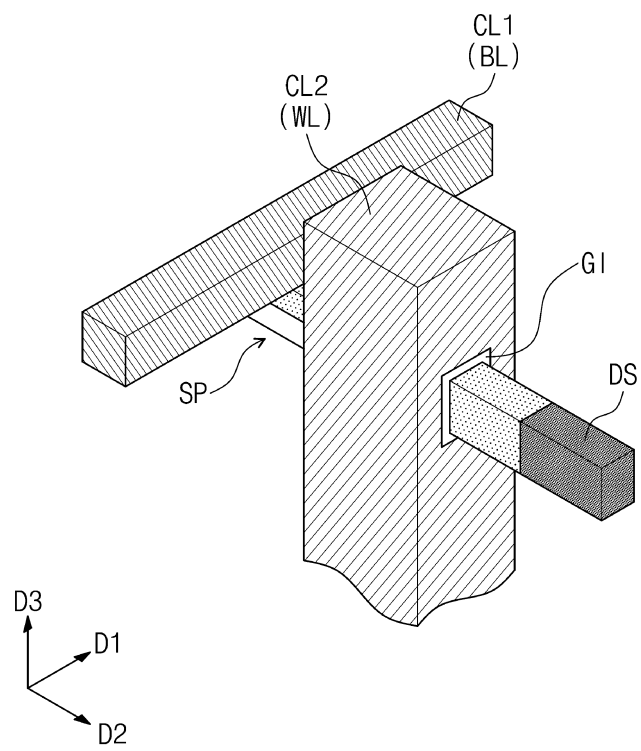


FIG. 9

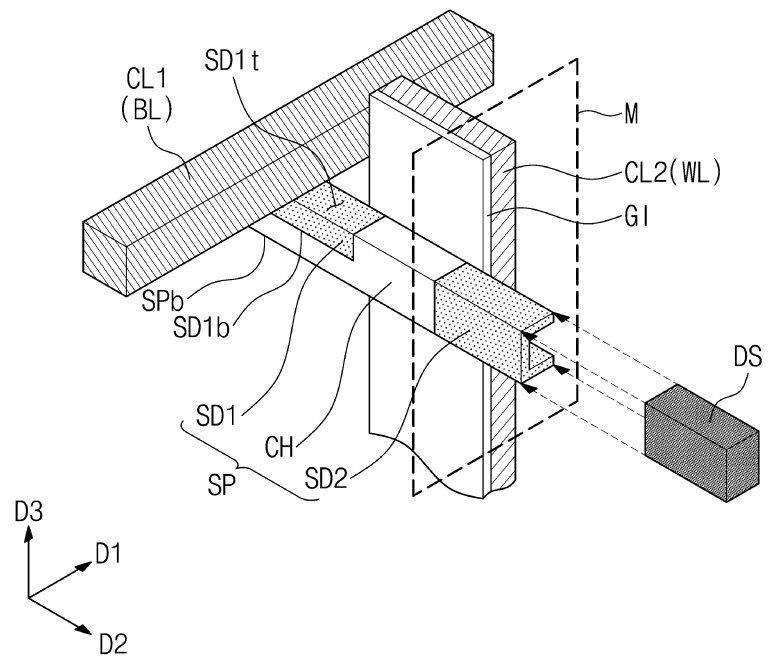


FIG. 10A

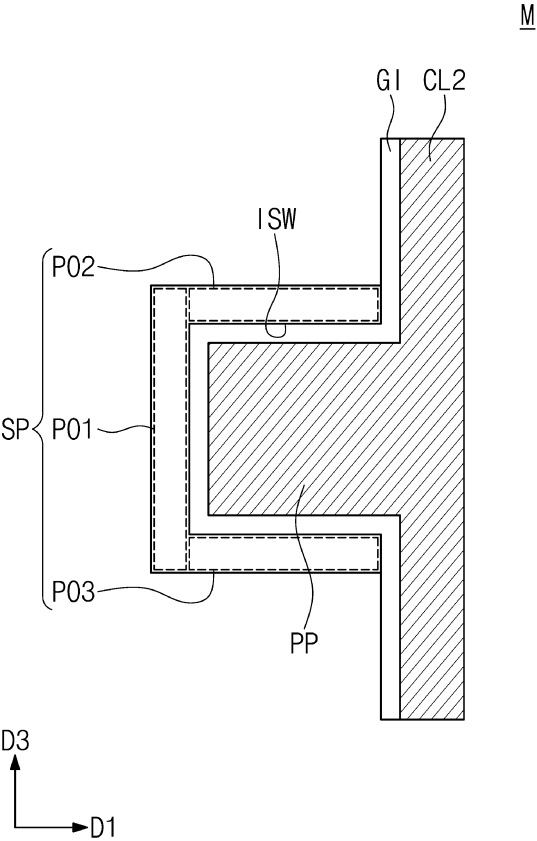


FIG. 10B

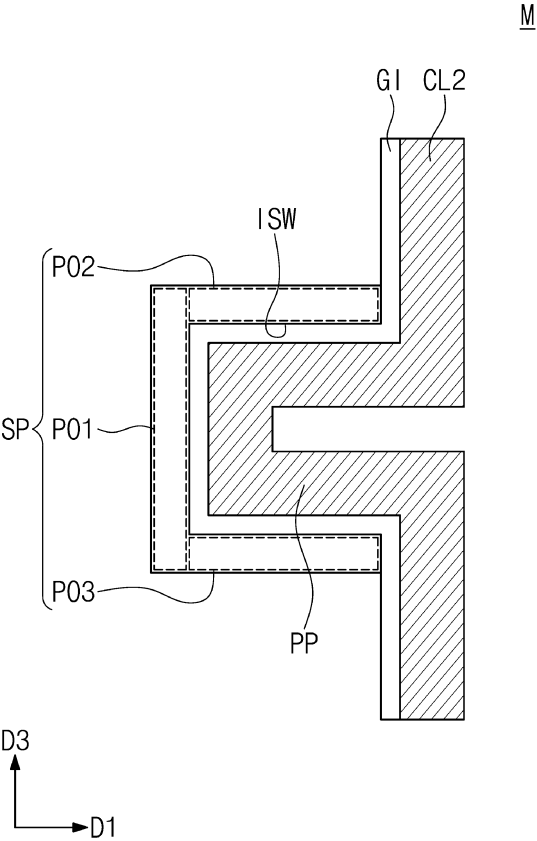


FIG. 11

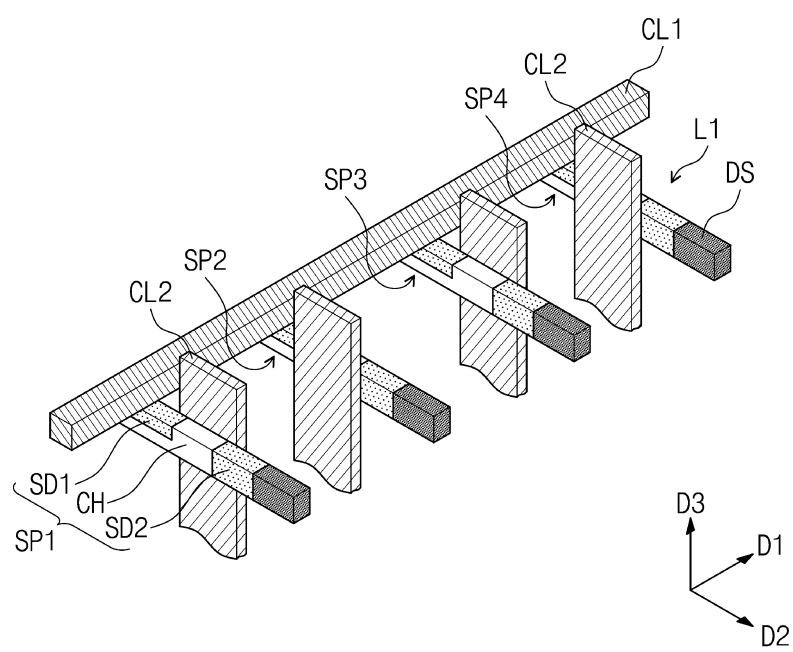


FIG. 12

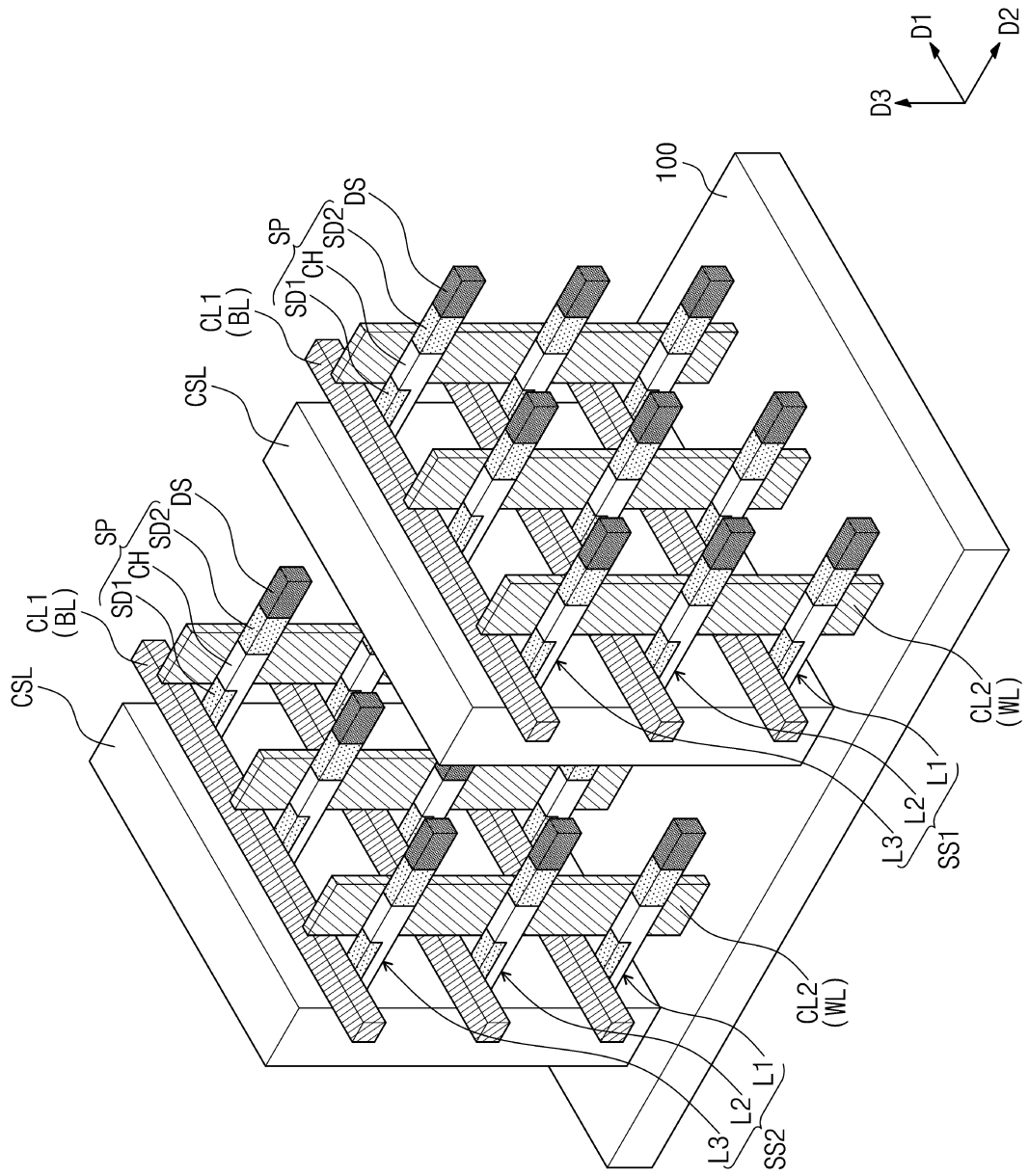


FIG. 13

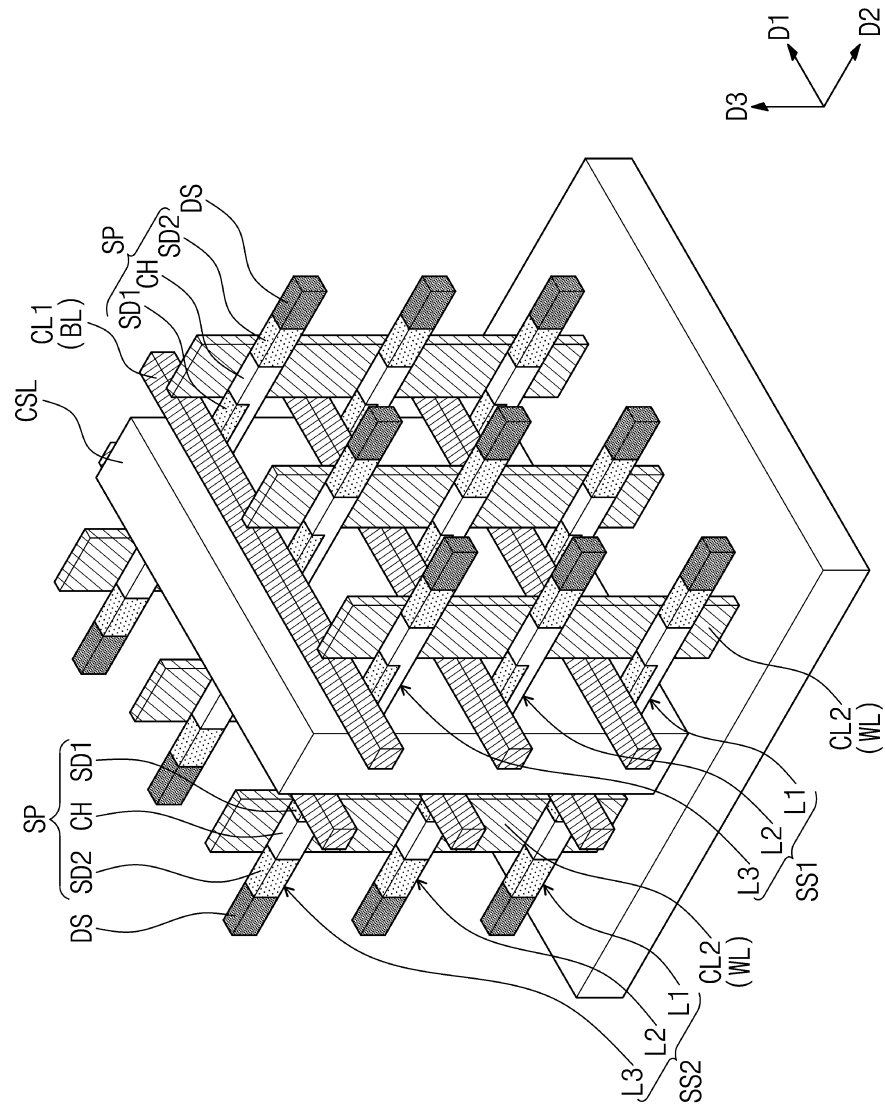


FIG. 14

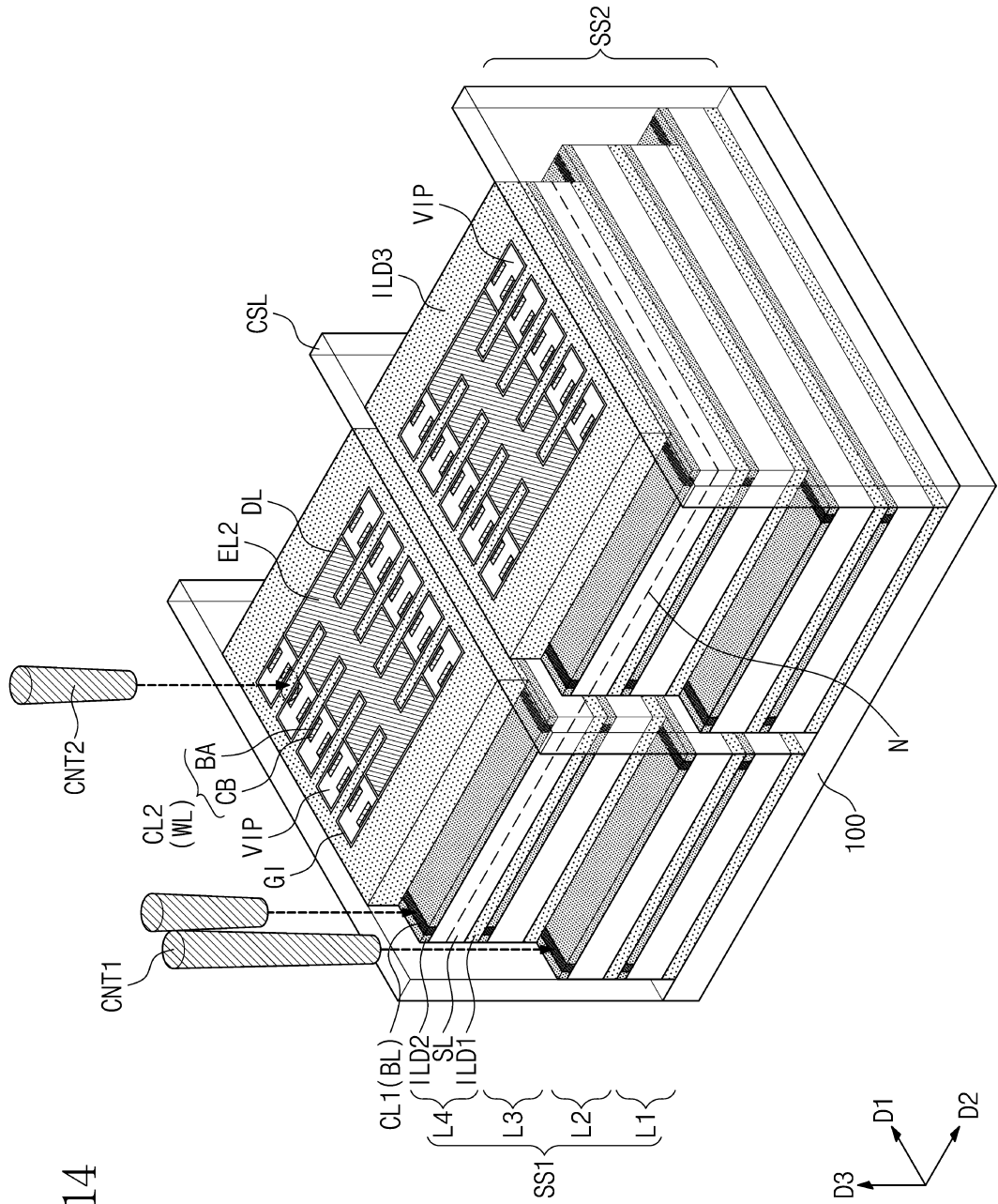


FIG. 15

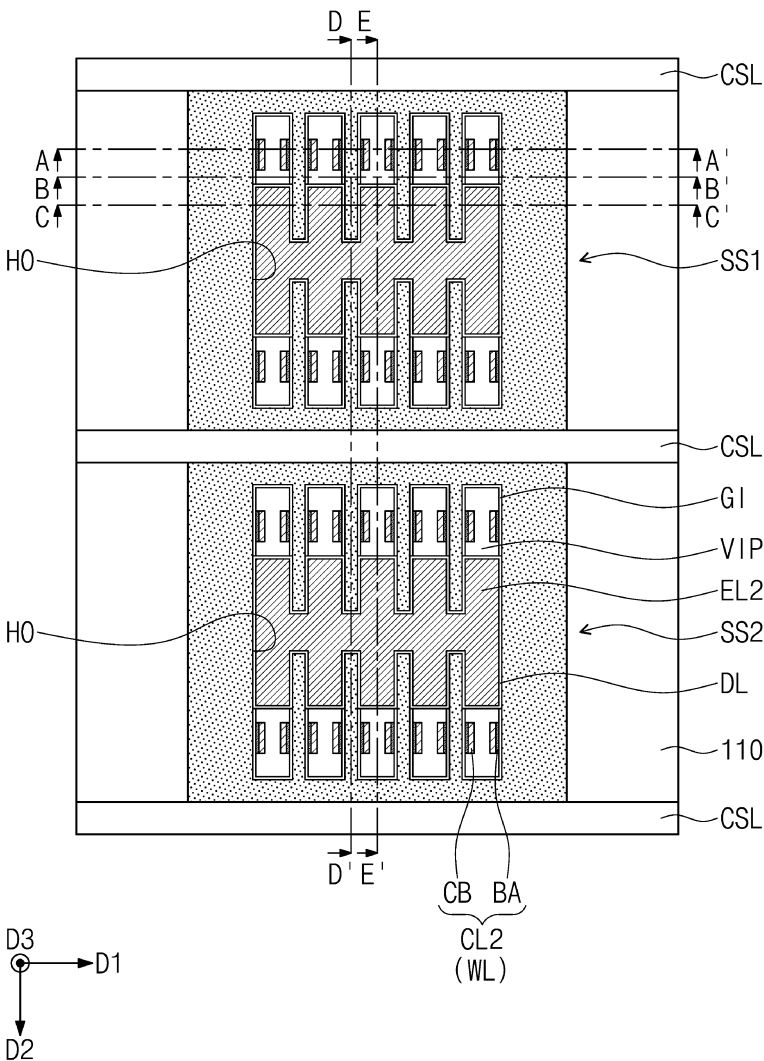


FIG. 16A

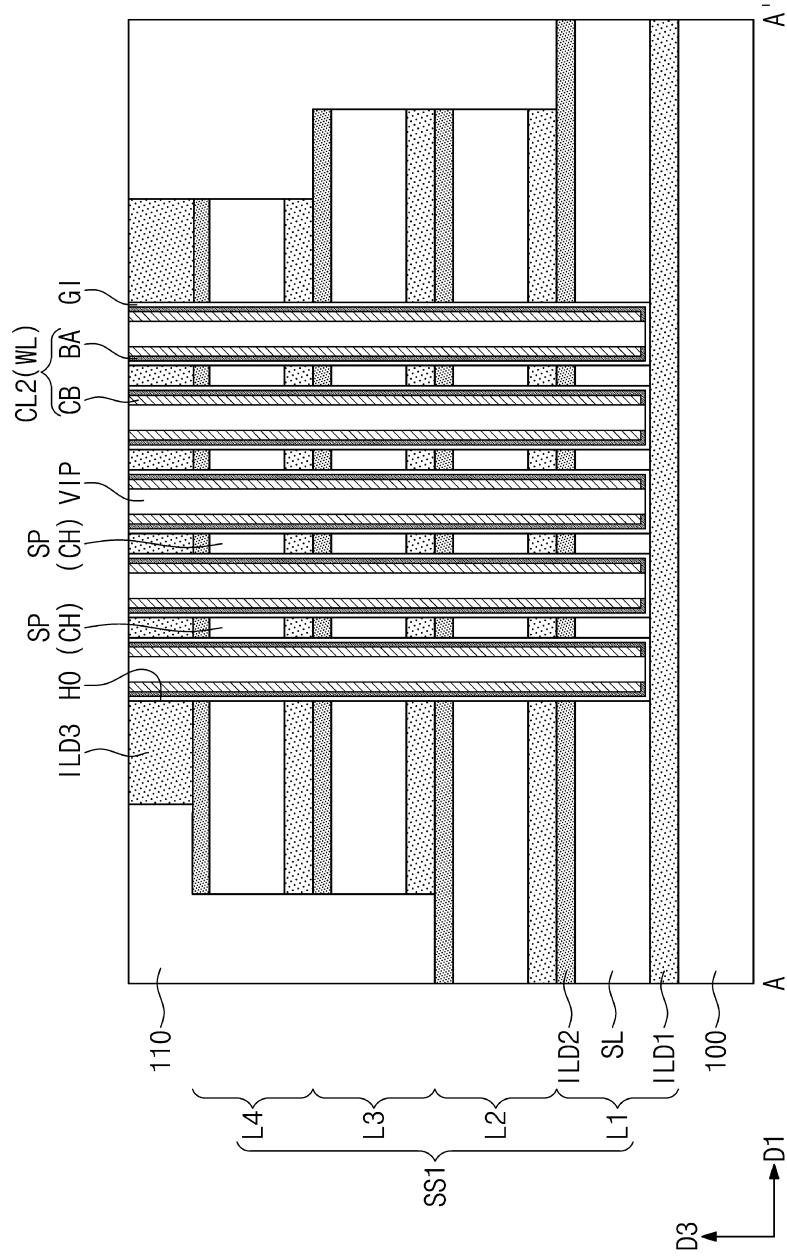


FIG. 16B

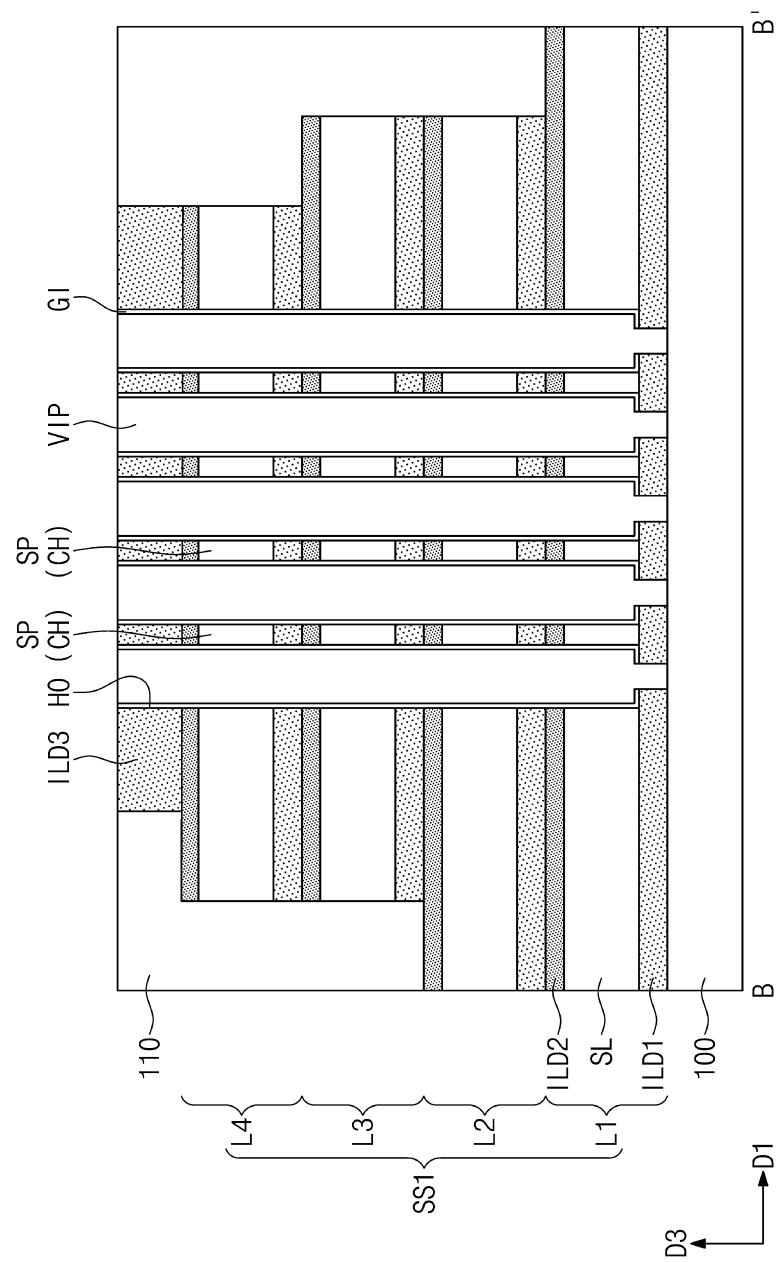


FIG. 16C

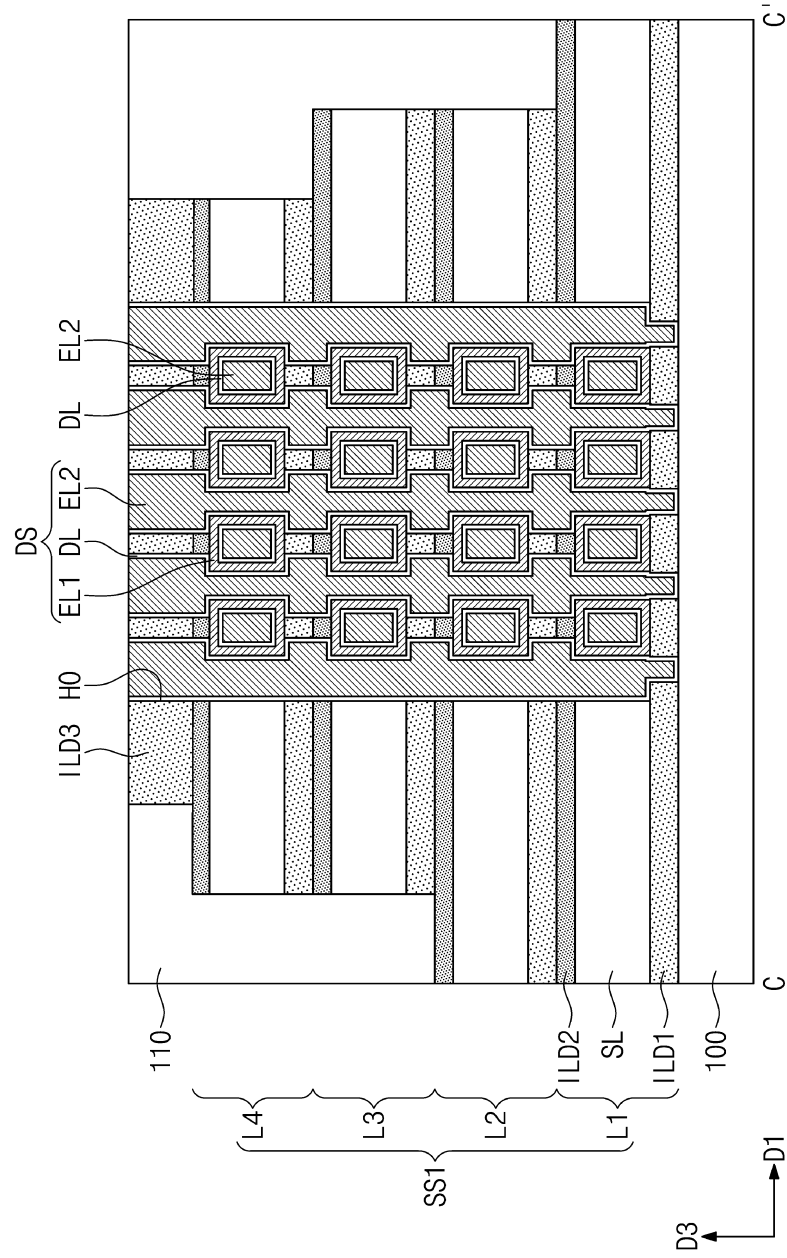


FIG. 16D

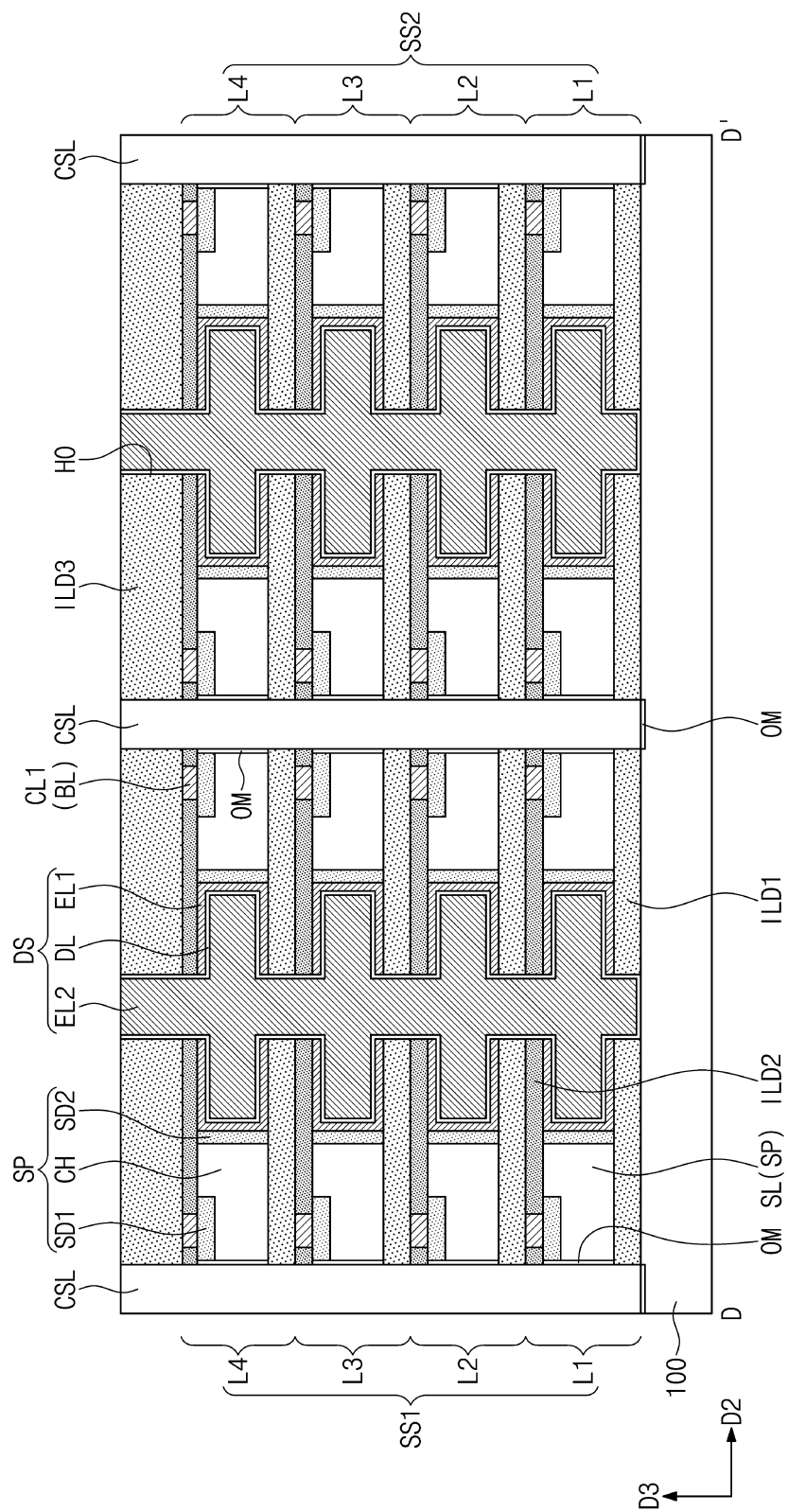


FIG. 16E

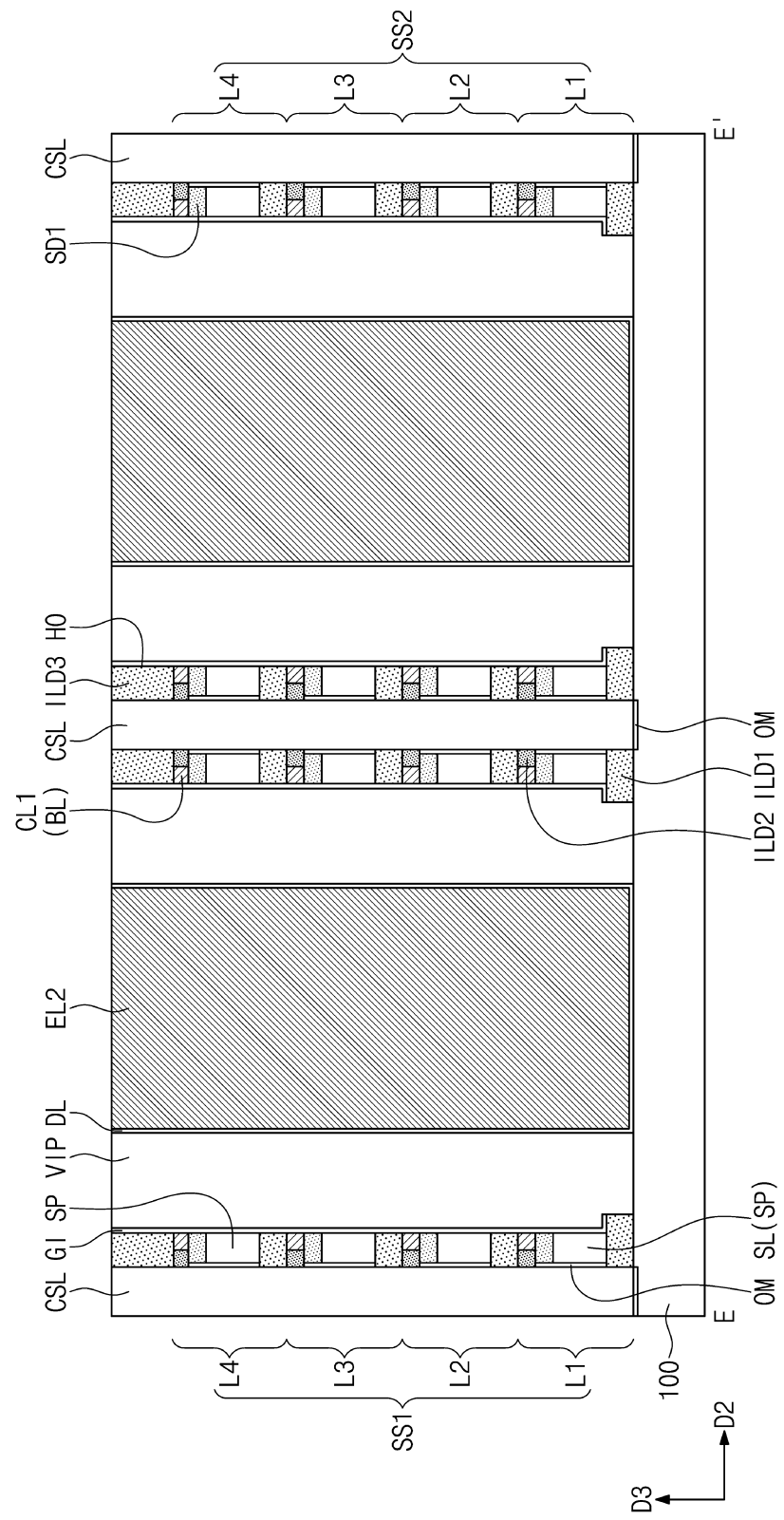


FIG. 17

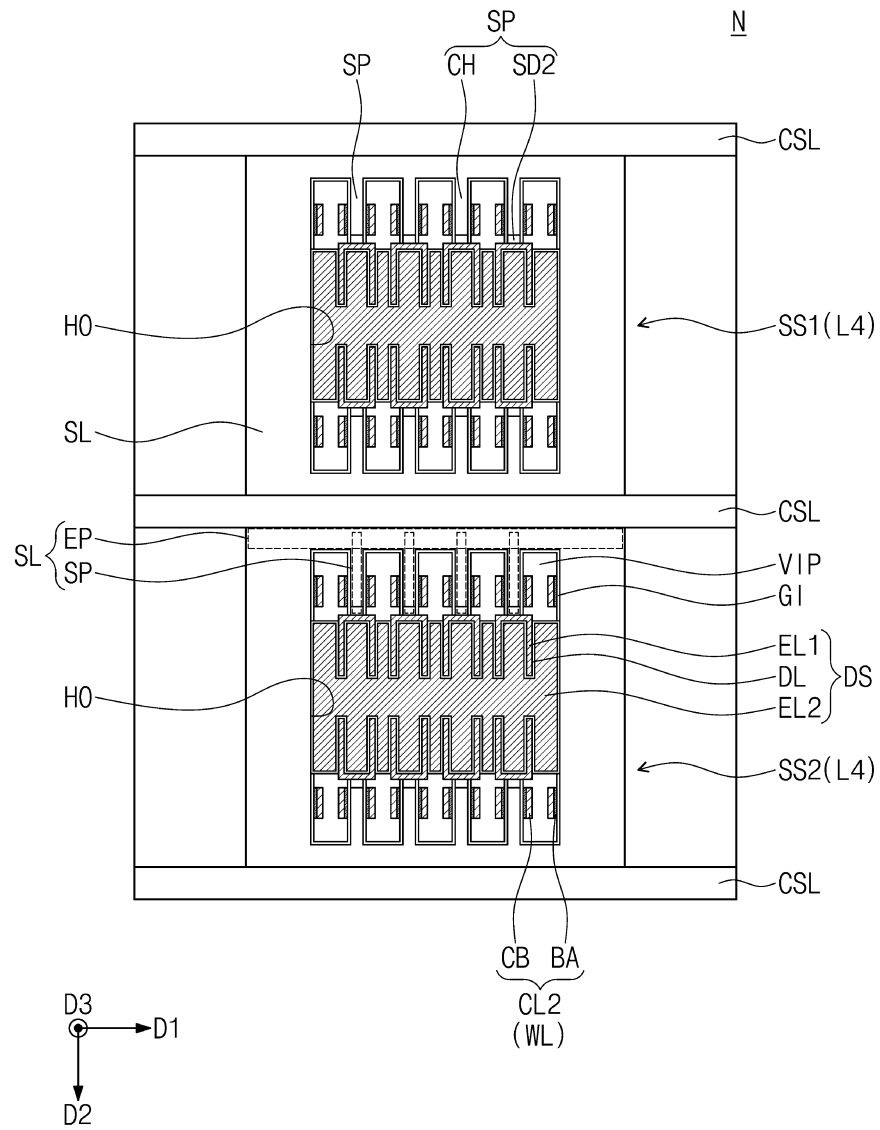


FIG. 18

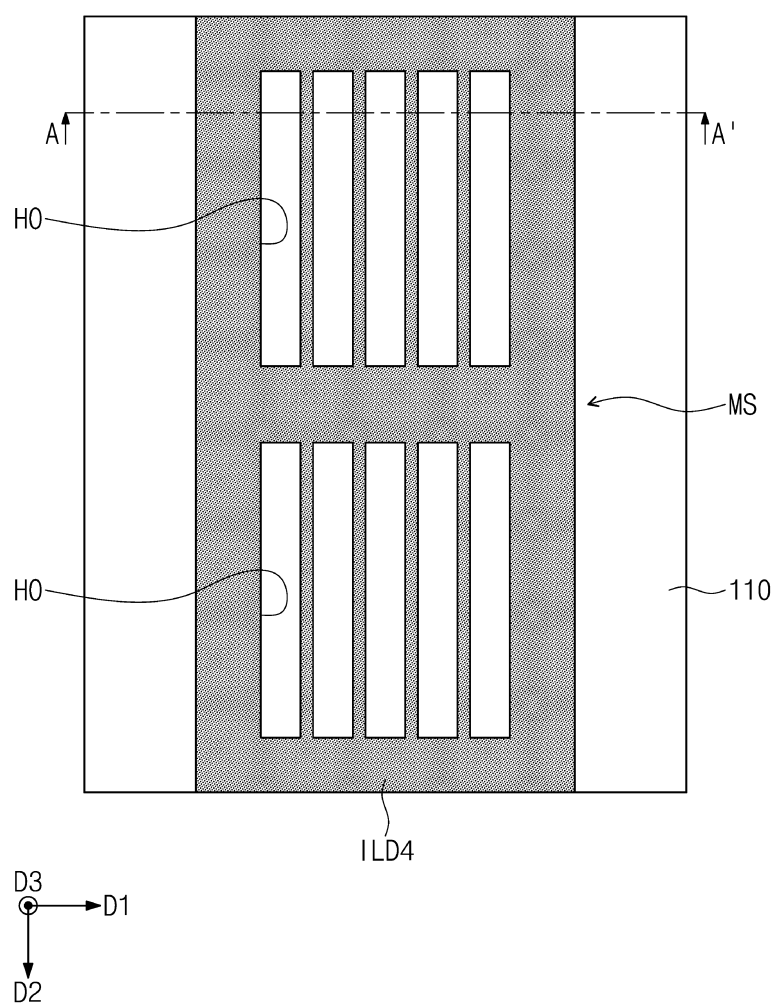


FIG. 19

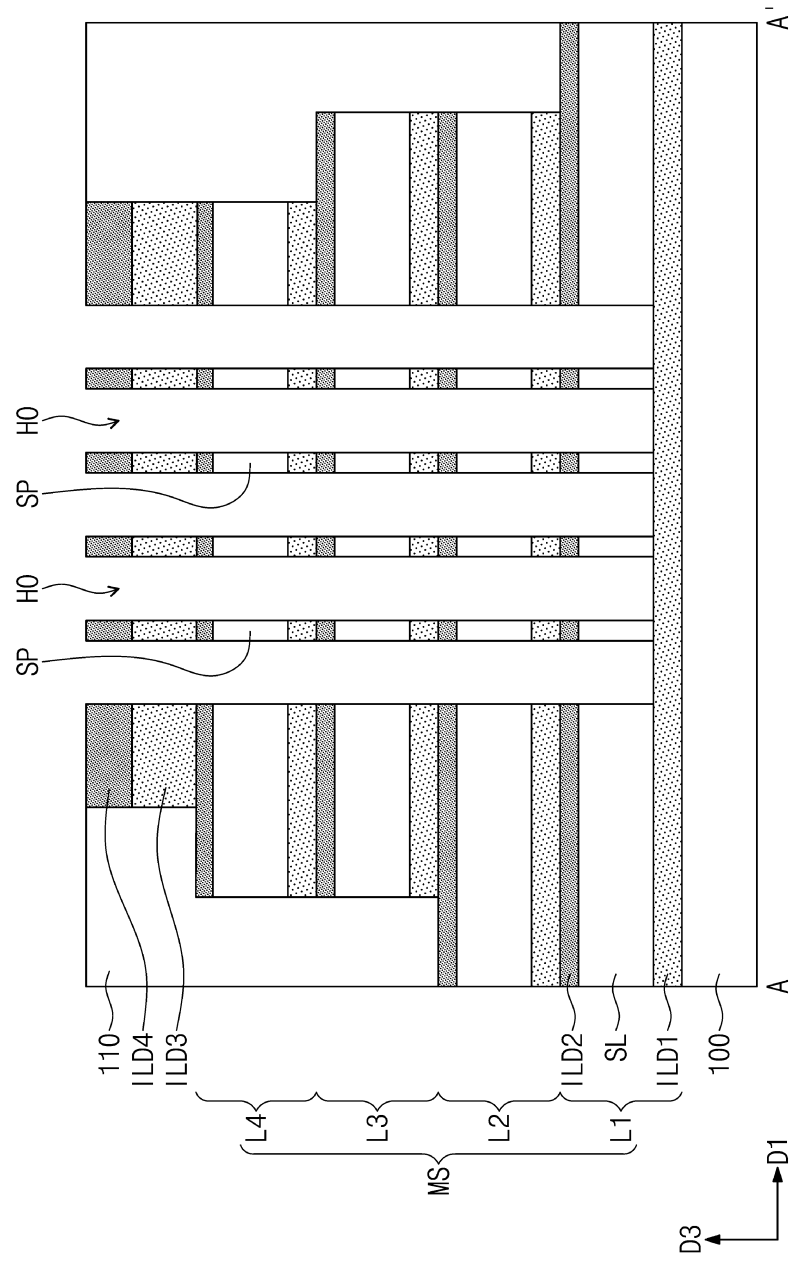


FIG. 20

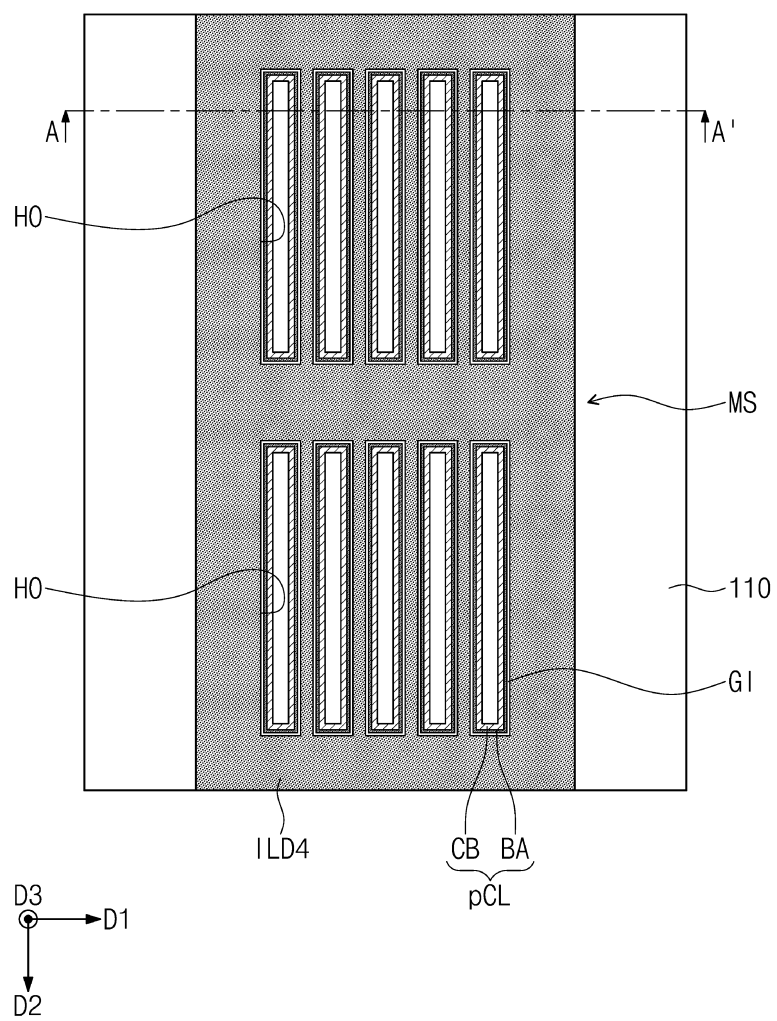


FIG. 21

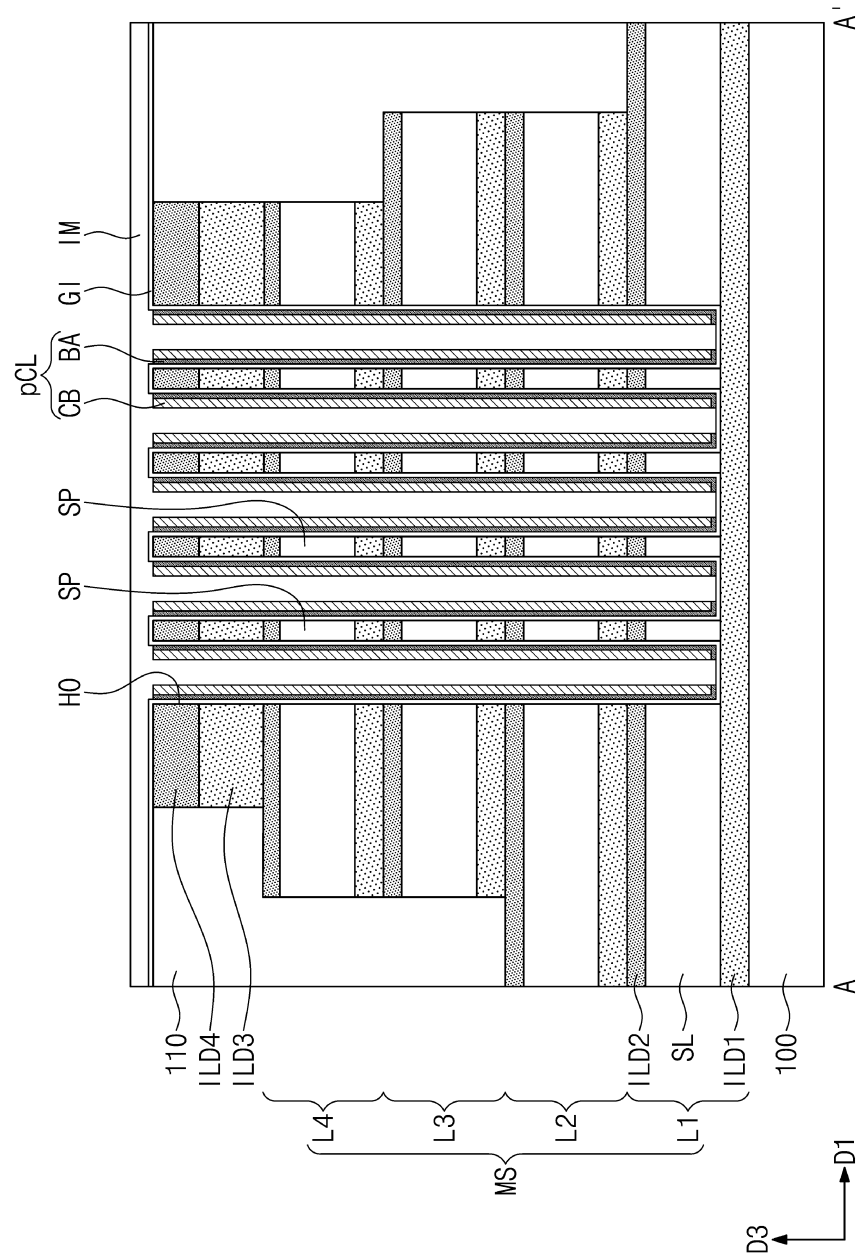


FIG. 22

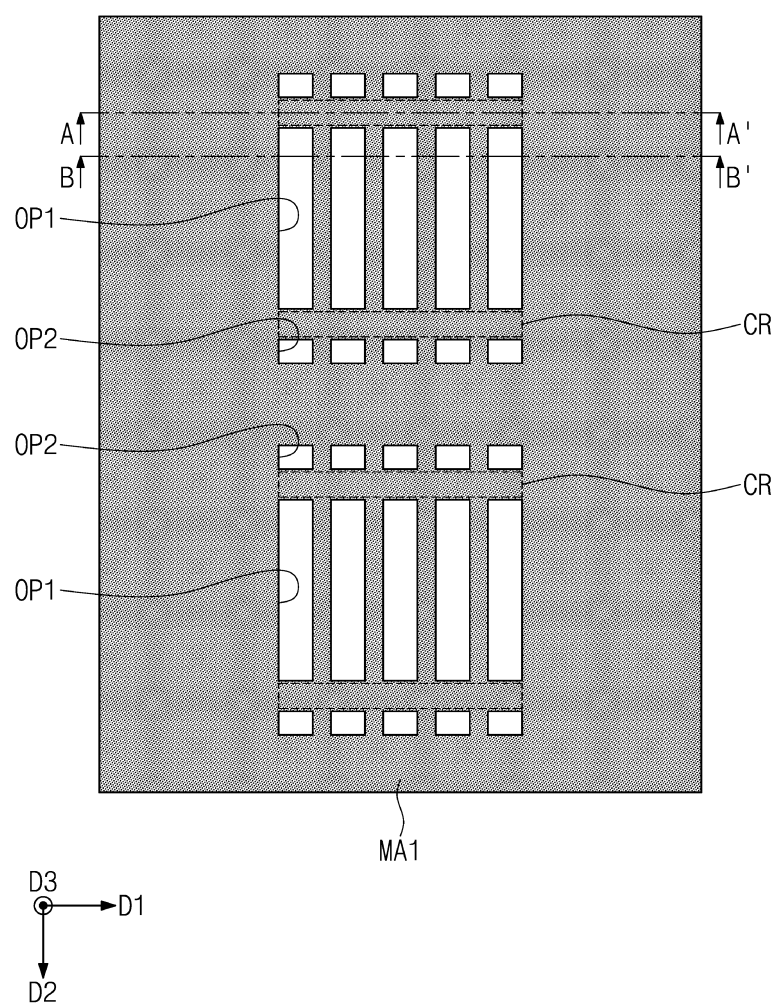


FIG. 23A

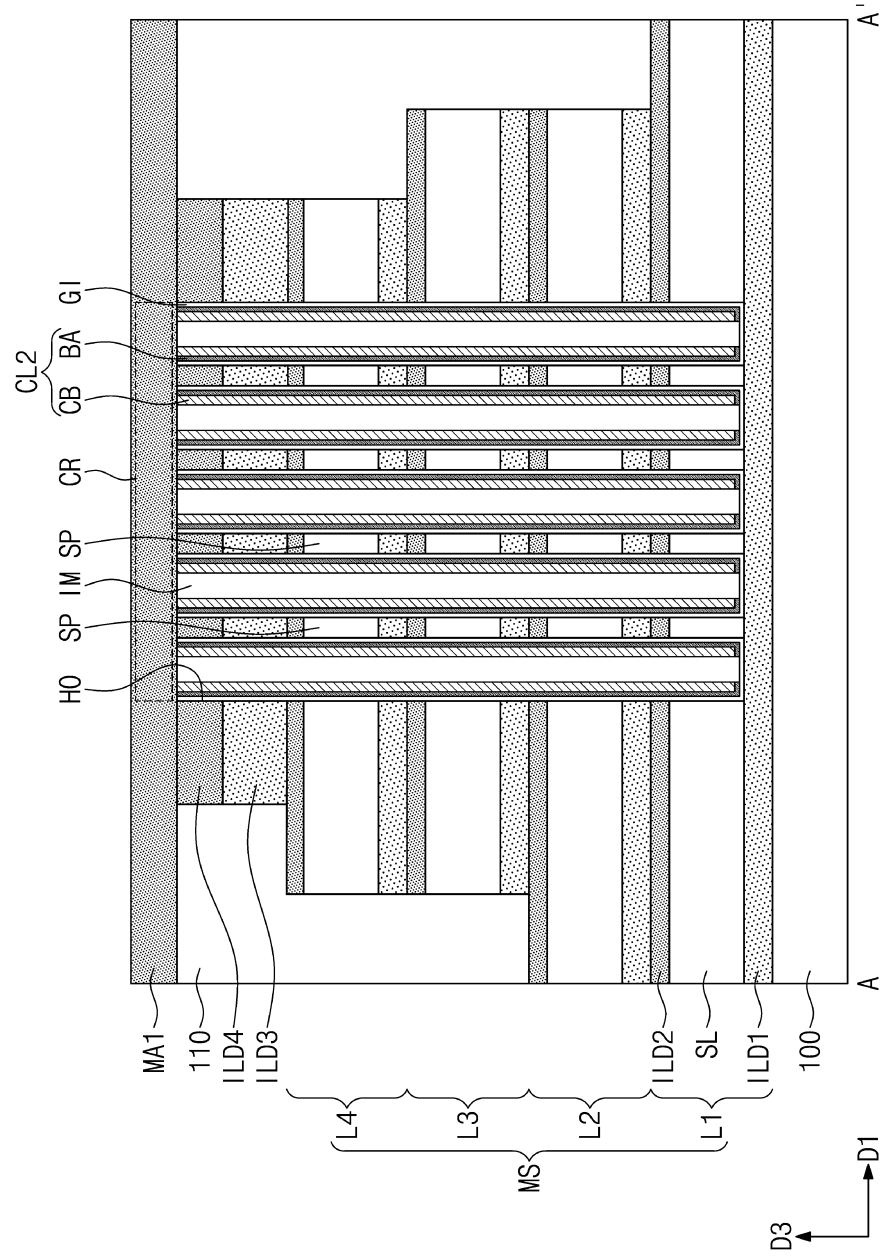


FIG. 23B

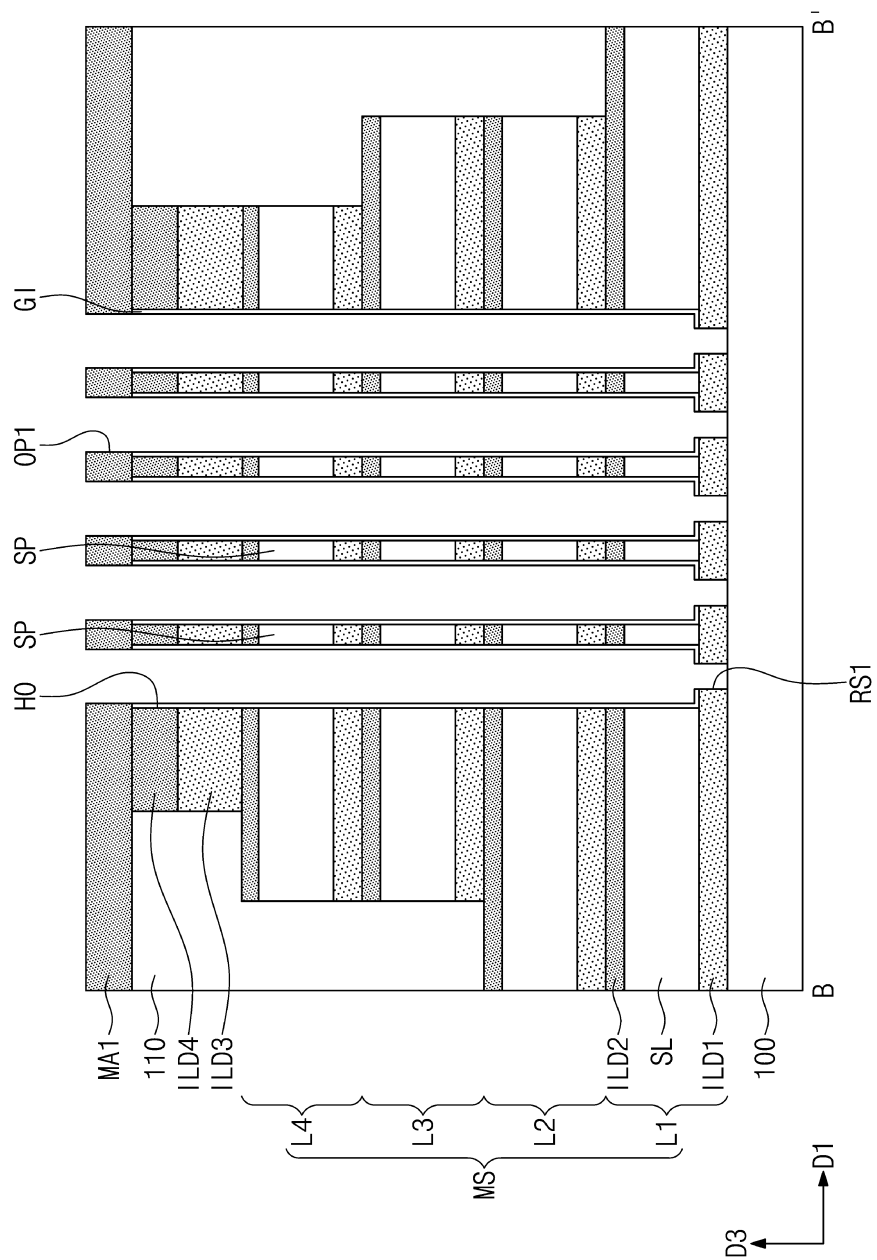


FIG. 24

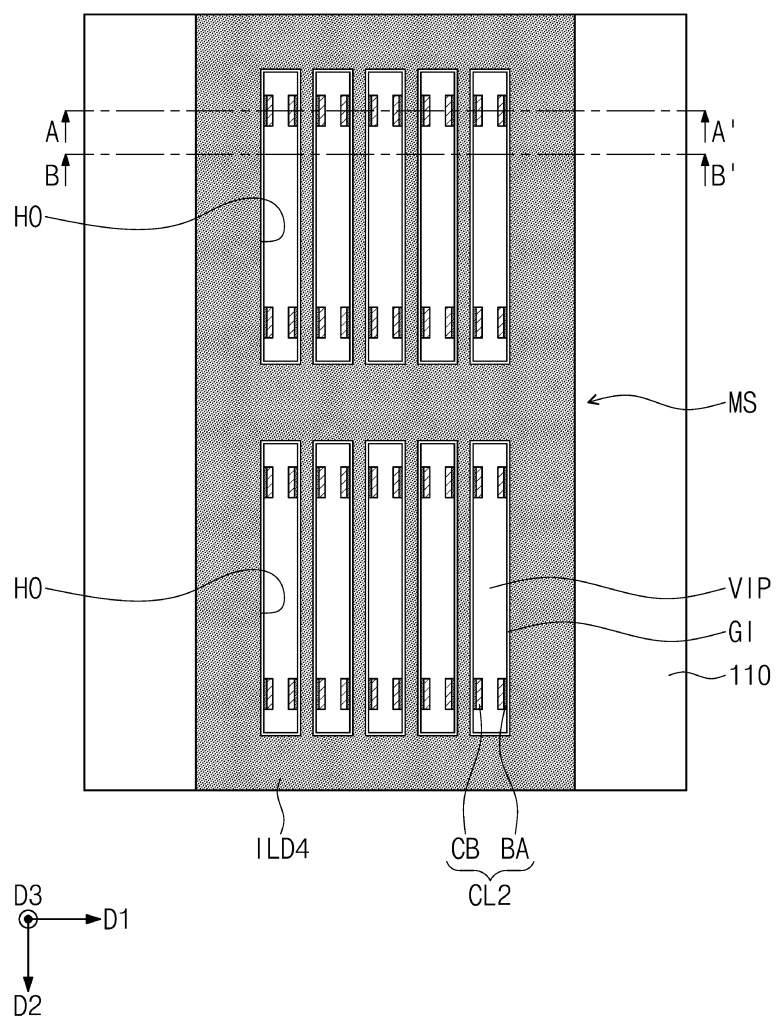


FIG. 25A

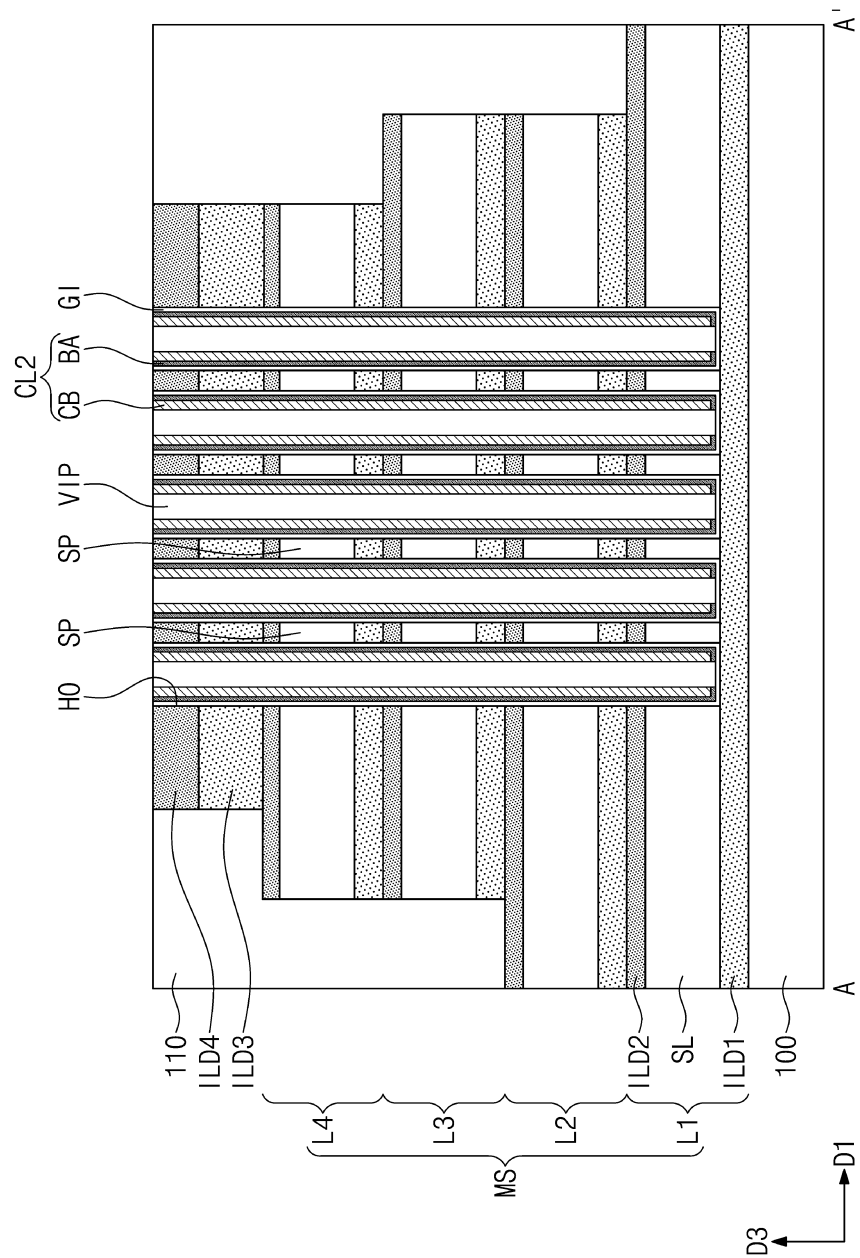


FIG. 25B

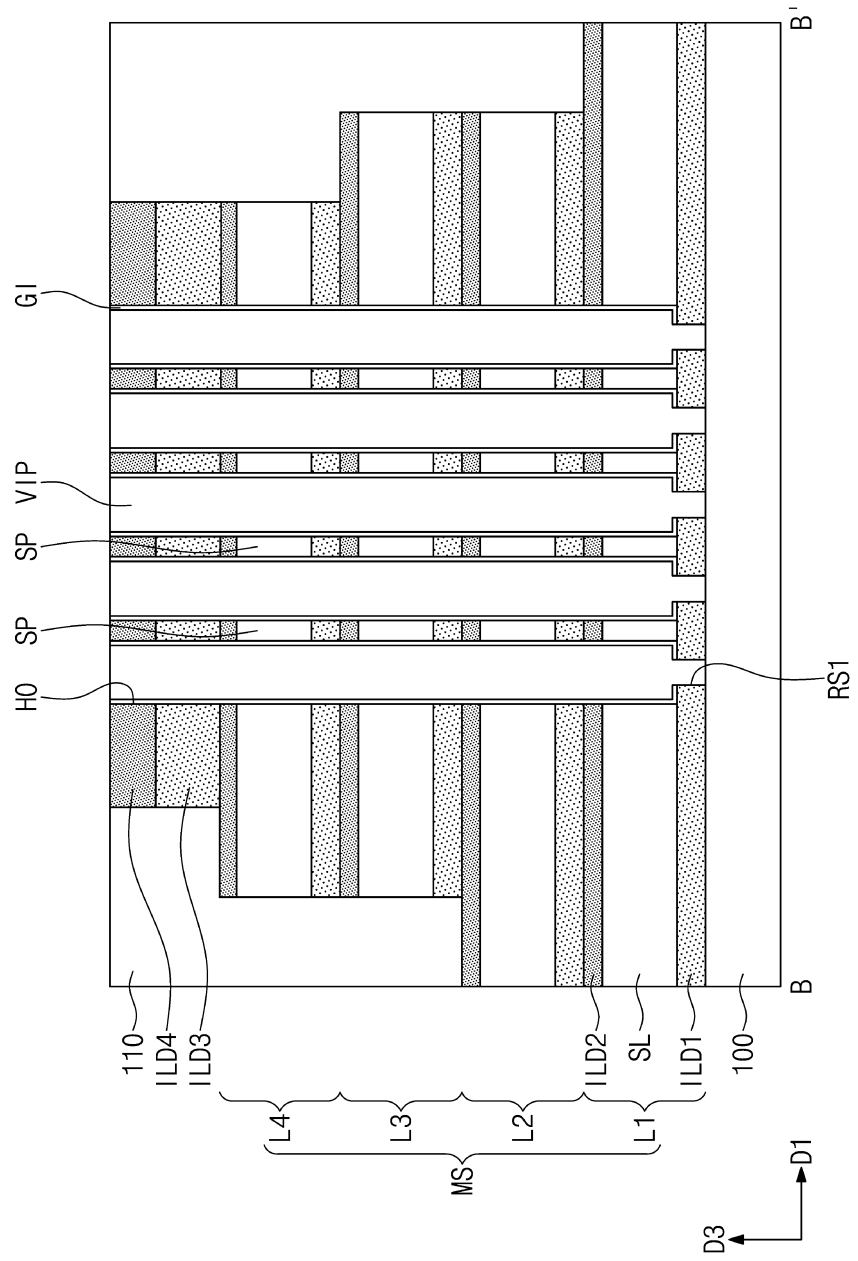


FIG. 26

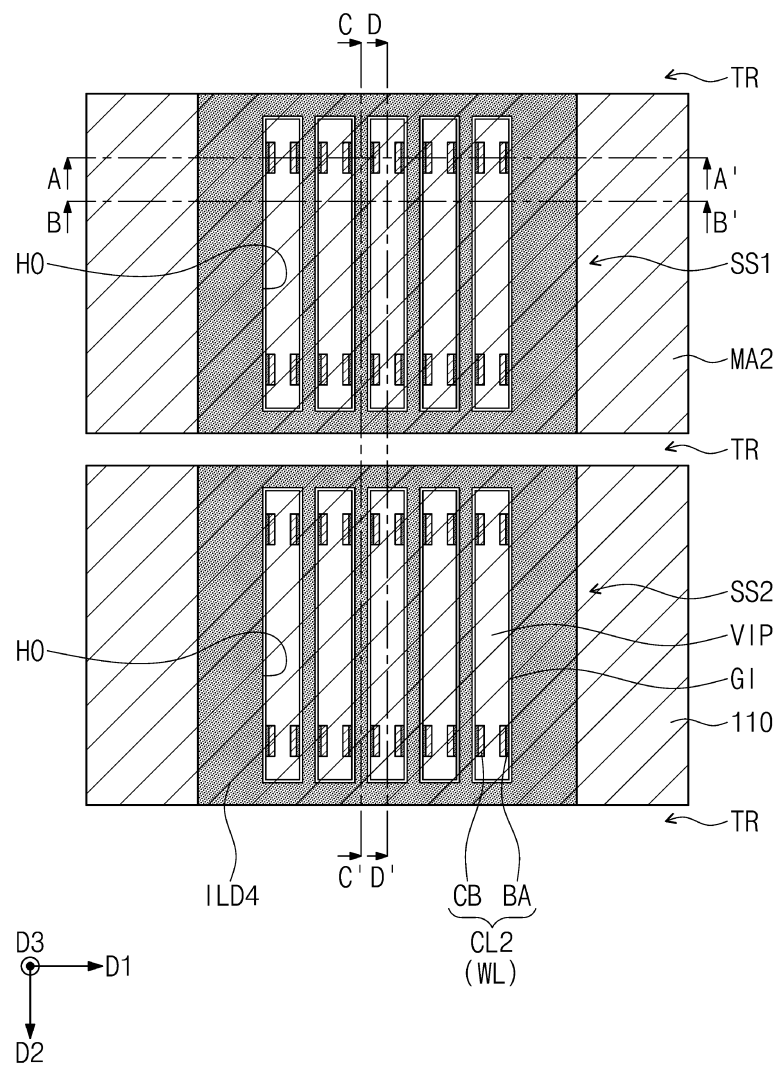


FIG. 27A

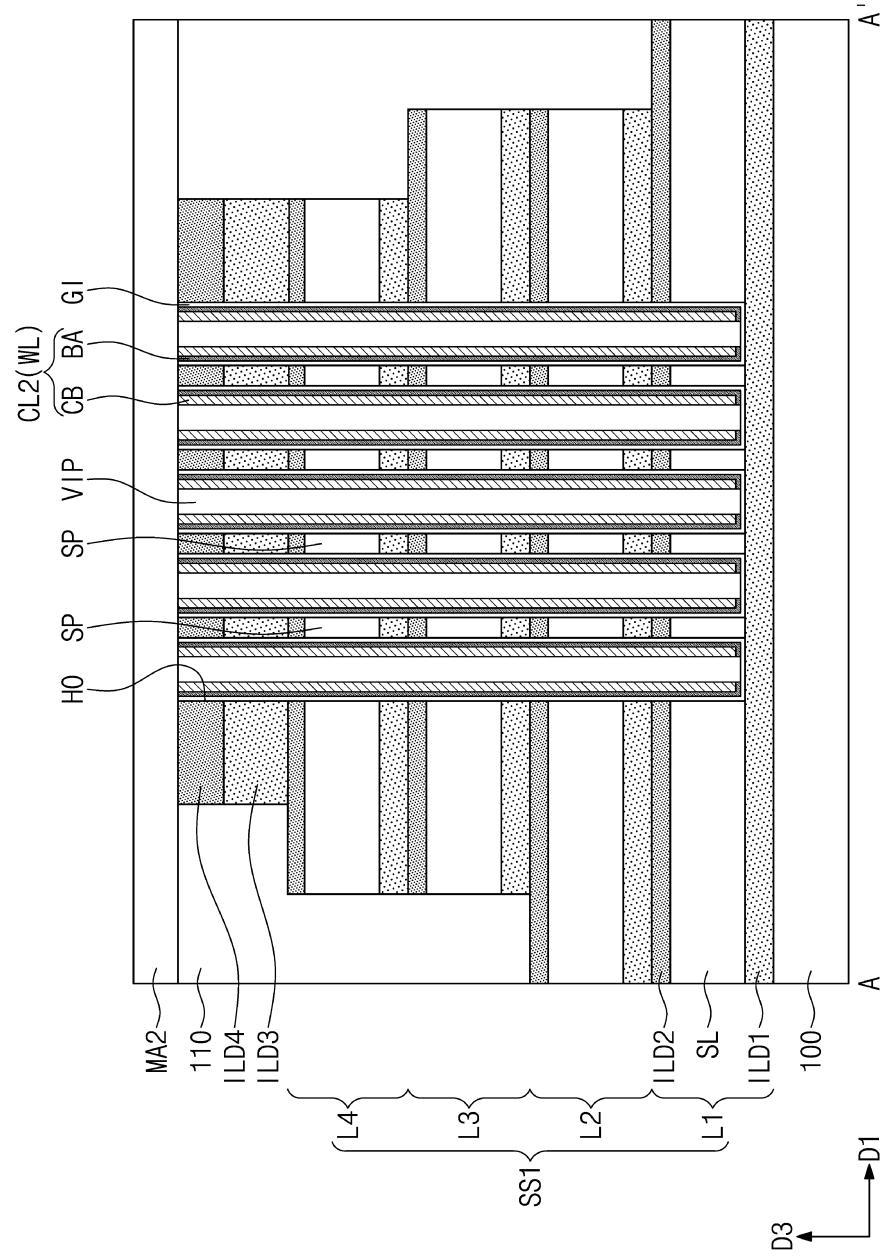


FIG. 27B

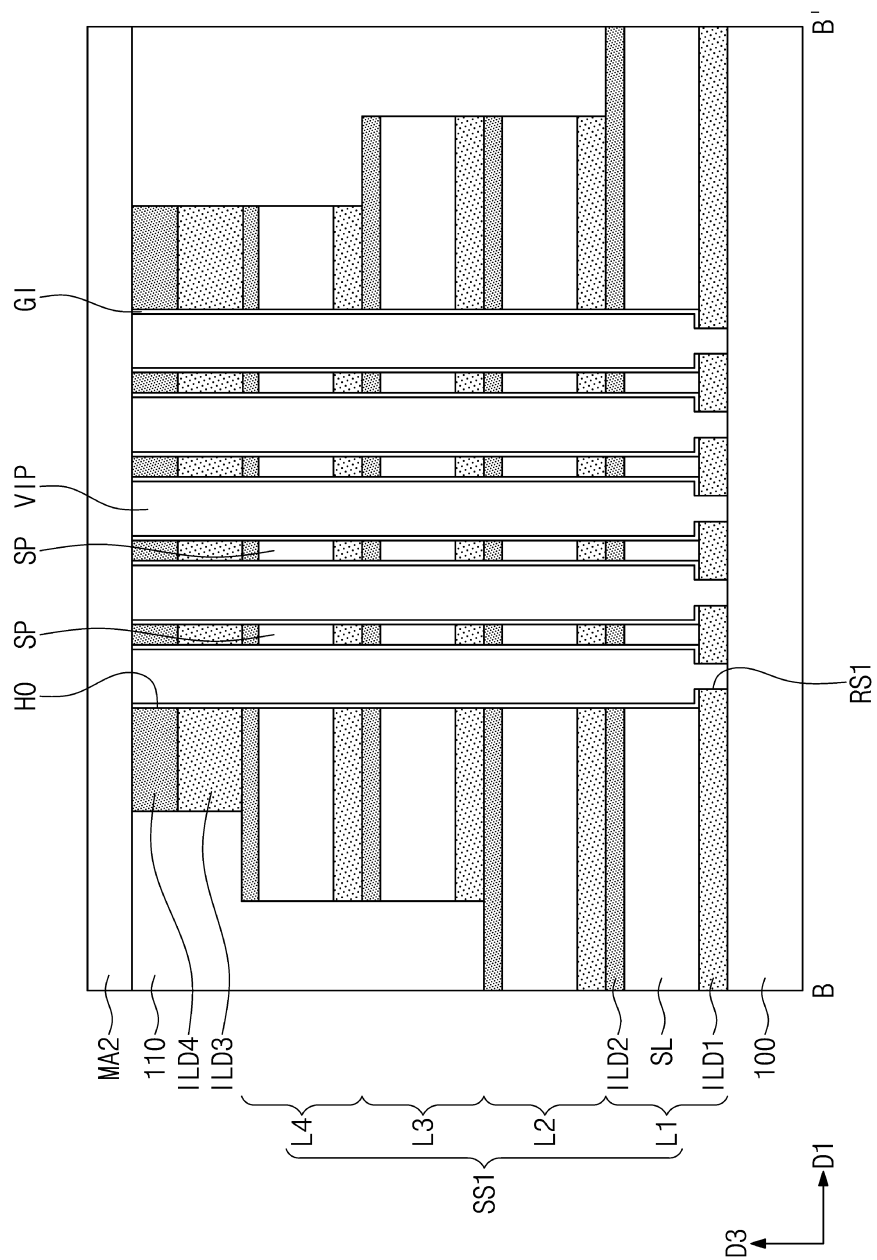


FIG. 27C

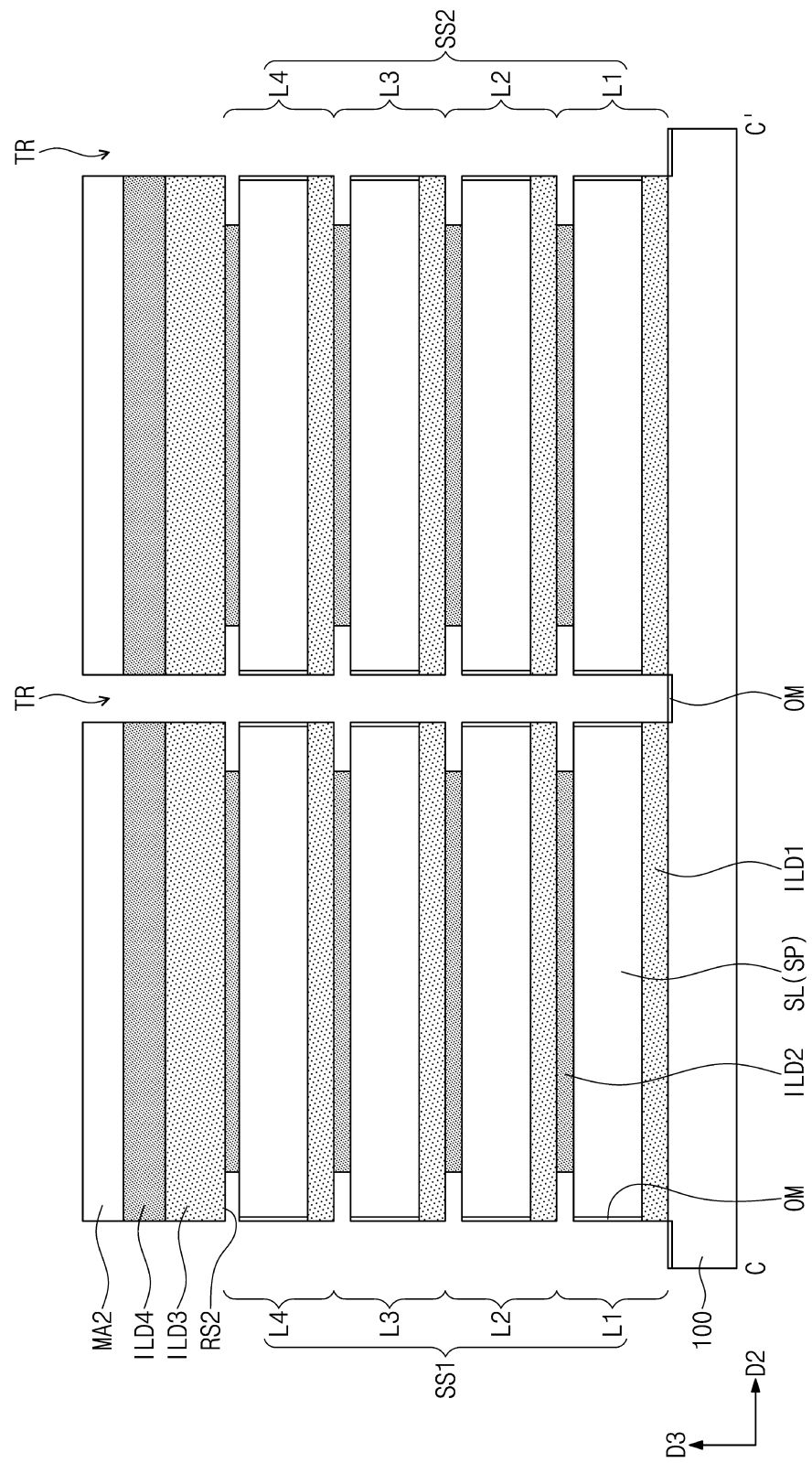


FIG. 27D

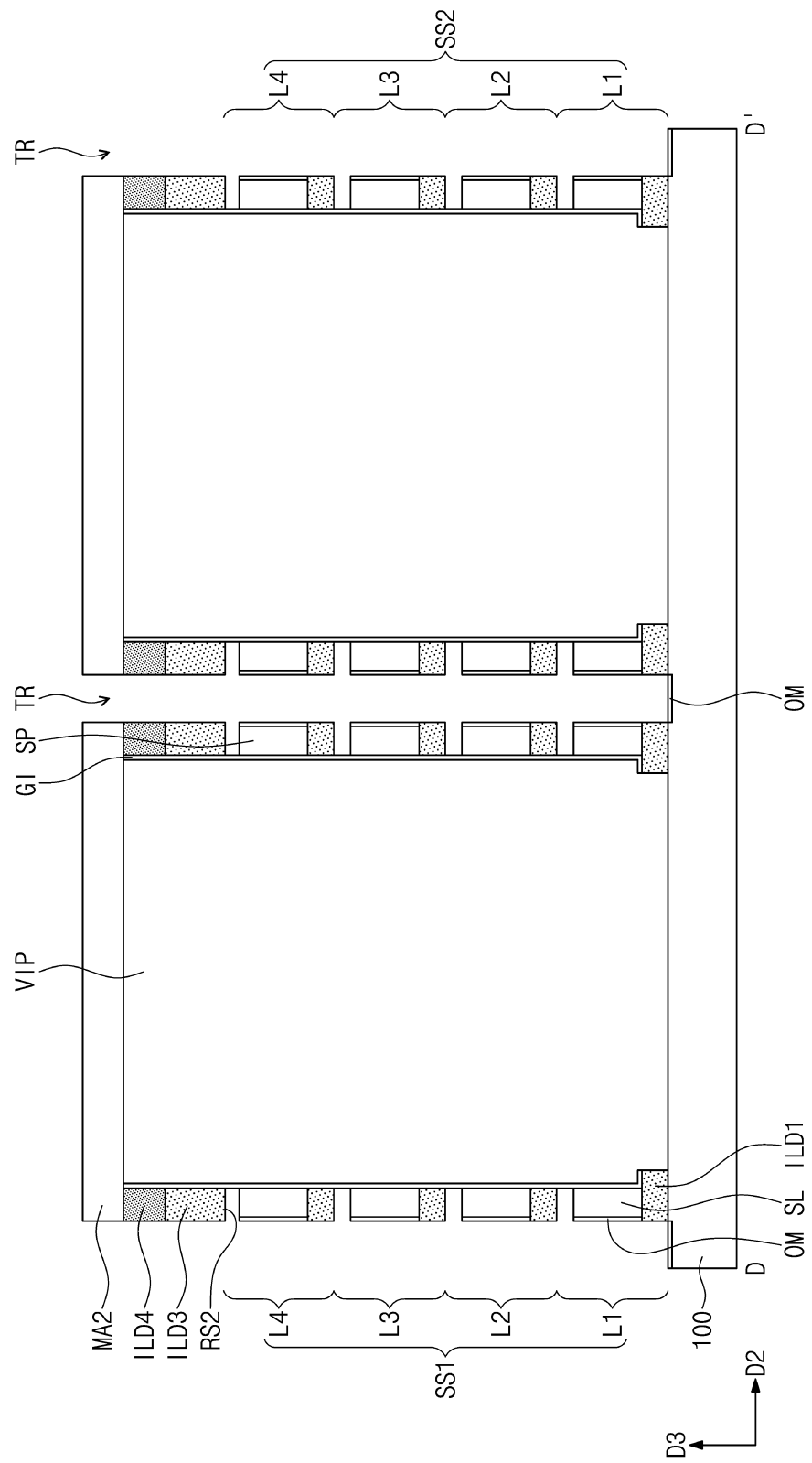
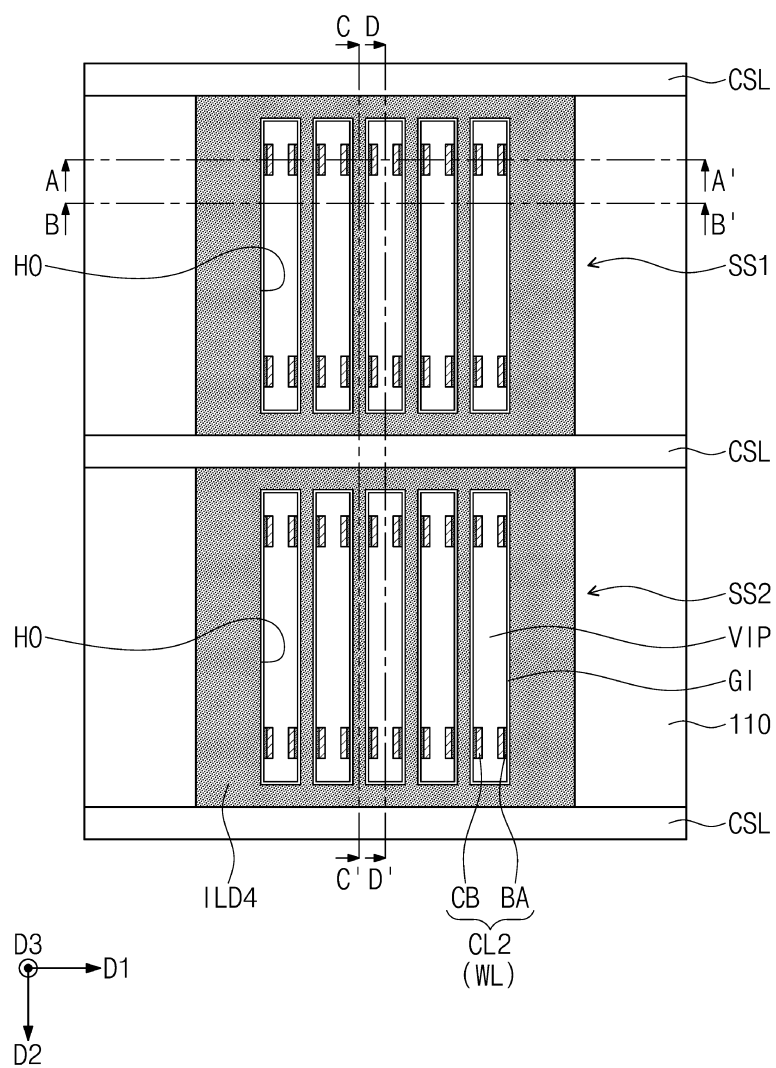


FIG. 28



This cross-sectional view shows a semiconductor device with a substrate 100. A series of layers are deposited on the substrate, including ILD1, SL, ILD2, and a stack of layers L1, L2, L3, and L4. The L1 layer contains a patterned layer 110. The L2, L3, and L4 layers contain a patterned layer 111. The device is divided into regions by a vertical line A-A'.

FIG. 29B

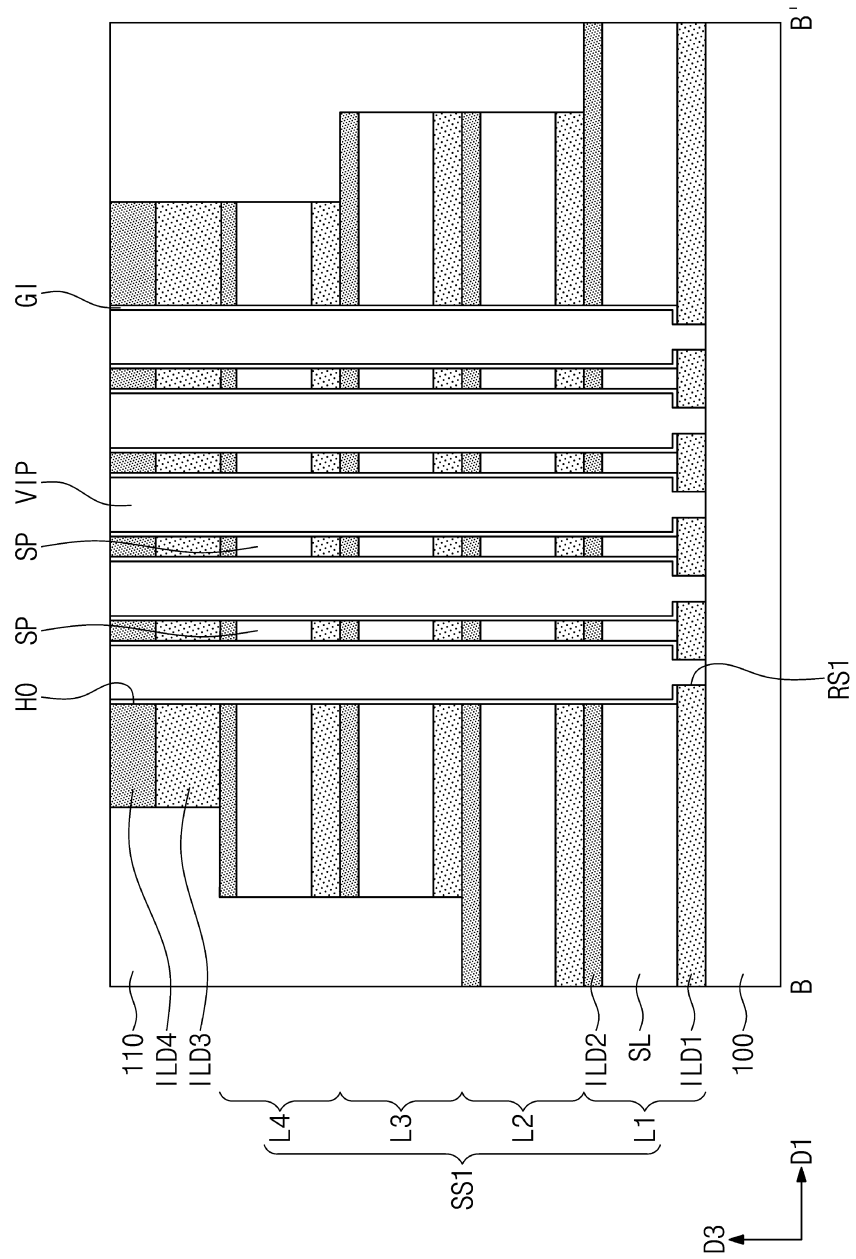


FIG. 29C

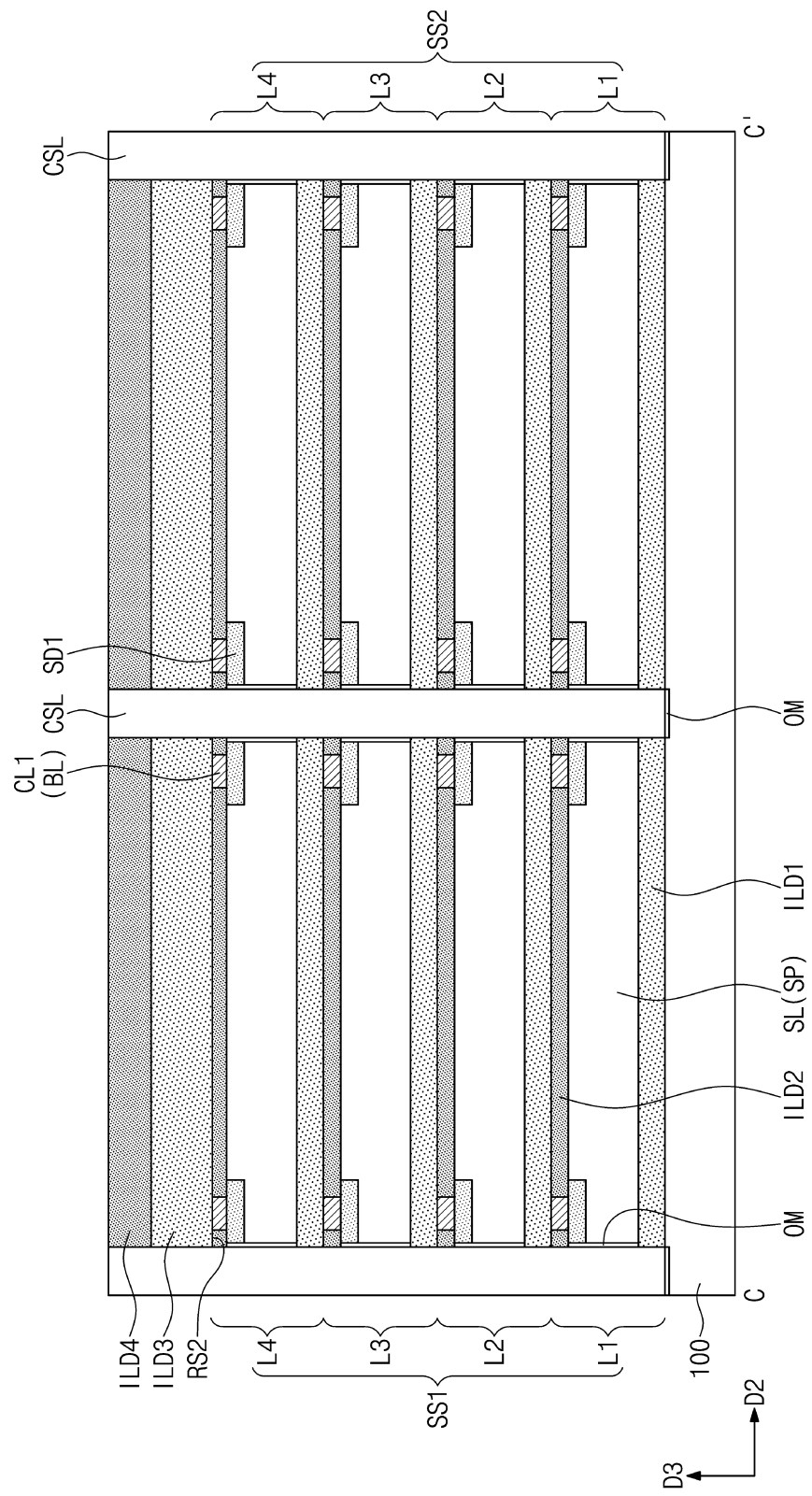


FIG. 29D

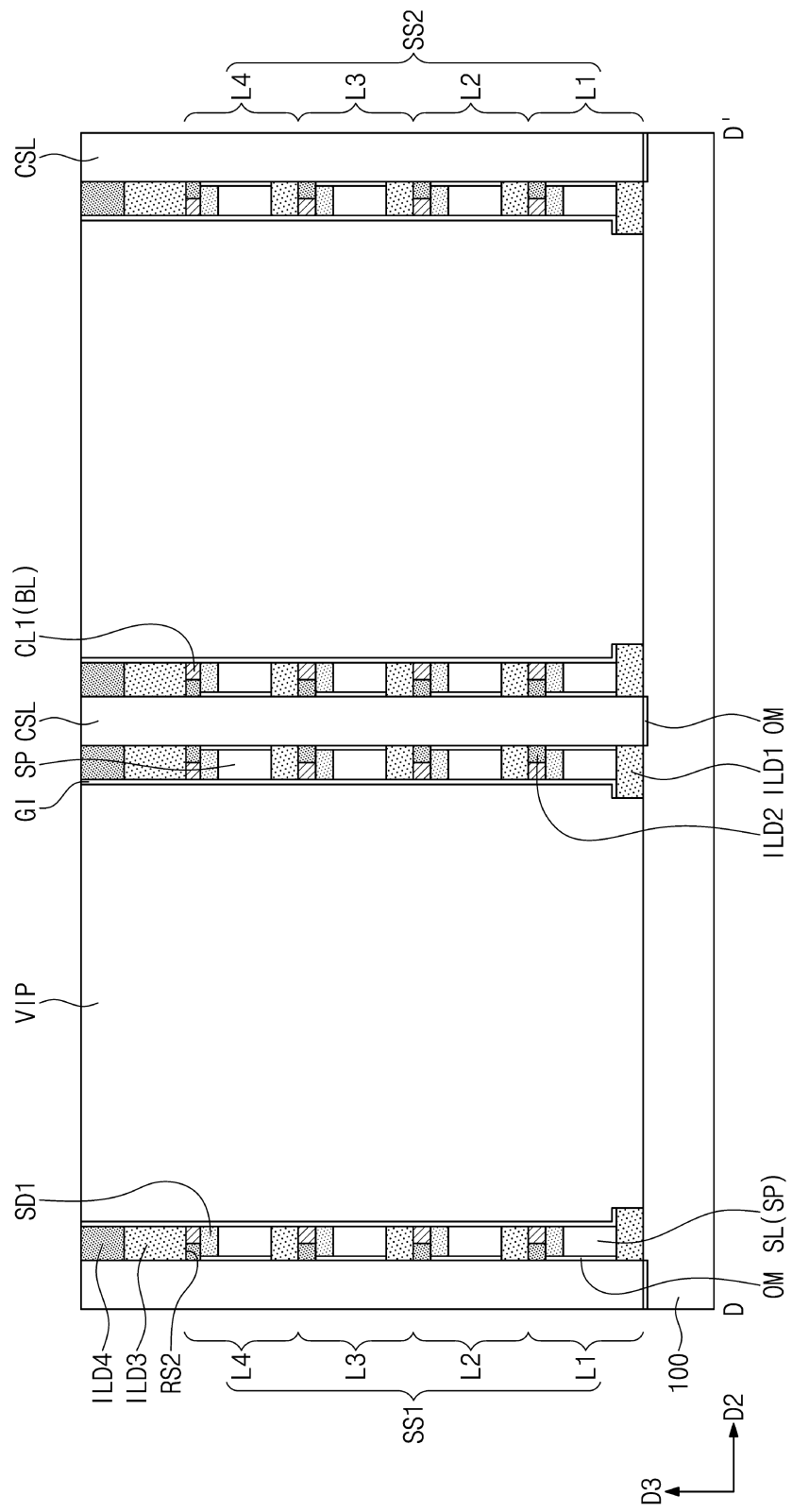


FIG. 30

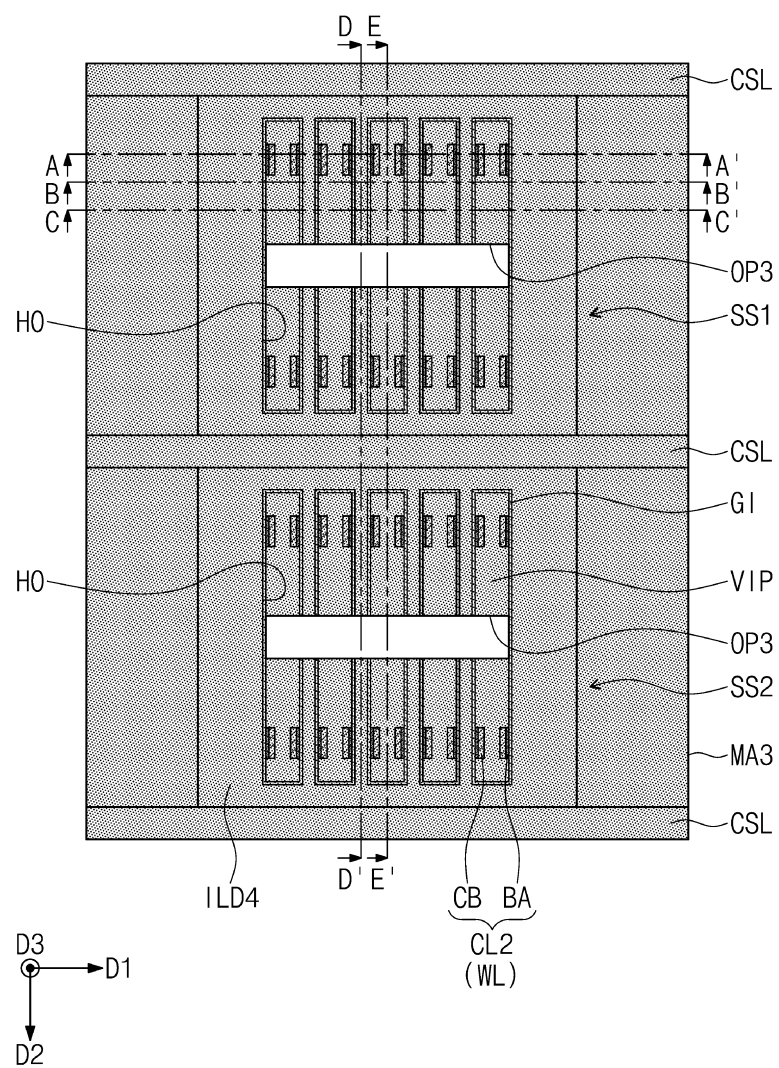


FIG. 31A

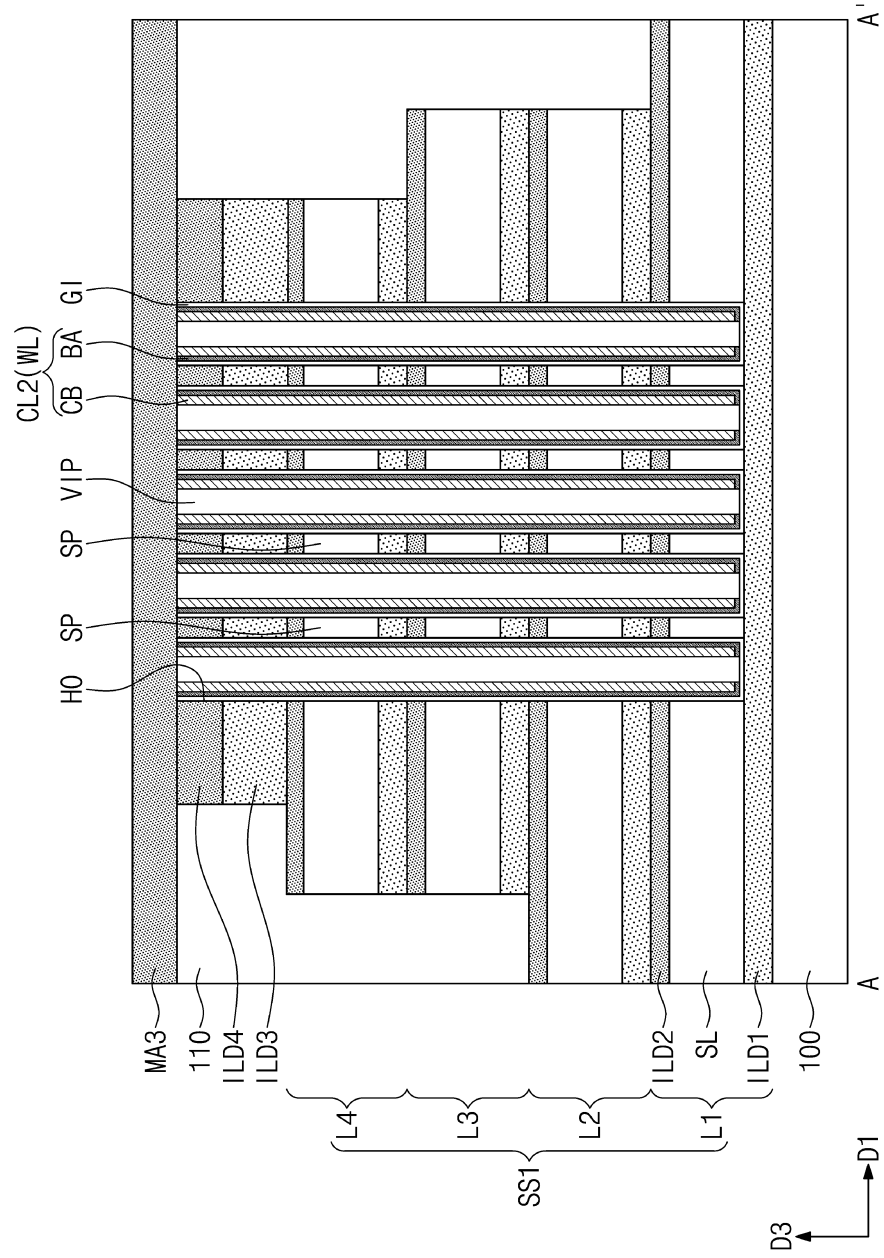


FIG. 31B

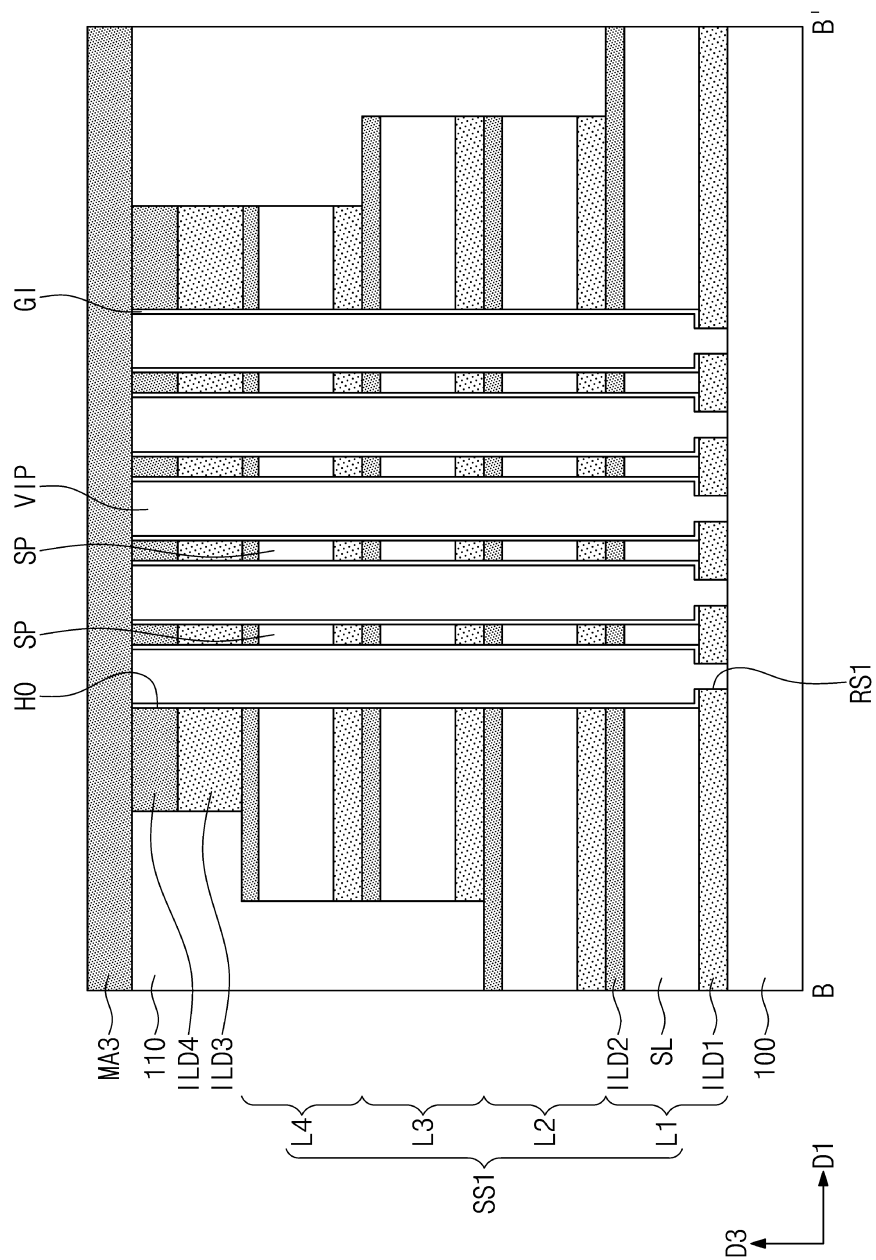


FIG. 31C

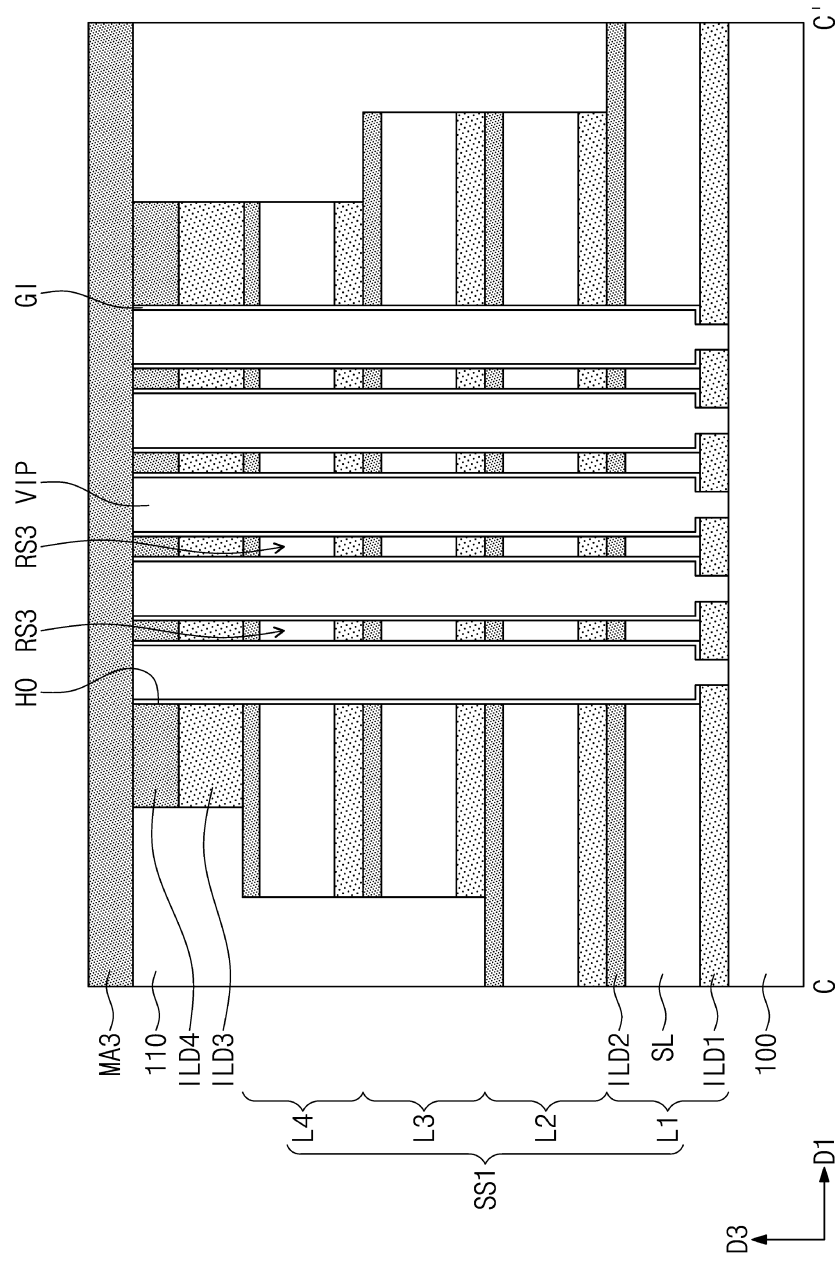


FIG. 31E

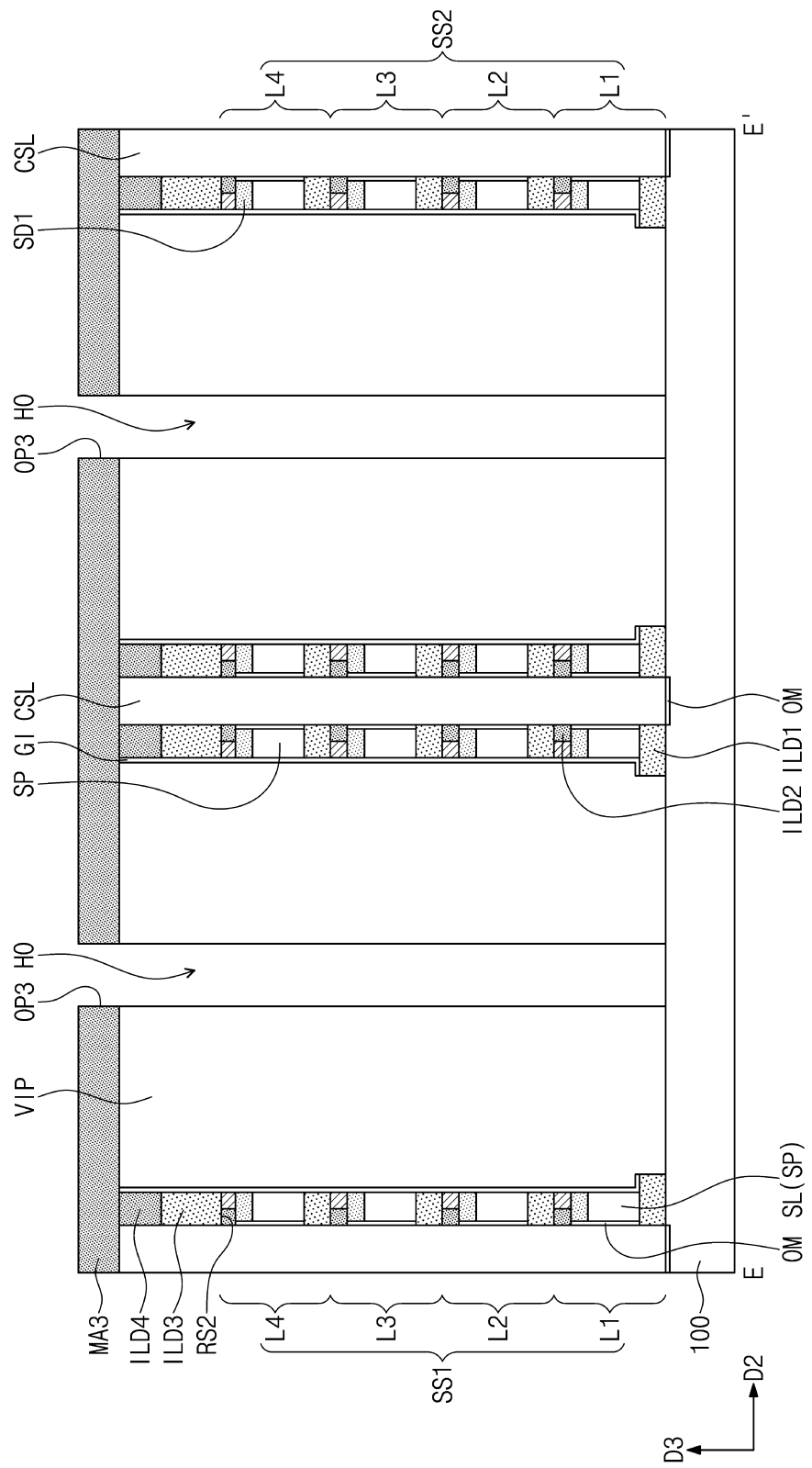


FIG. 32

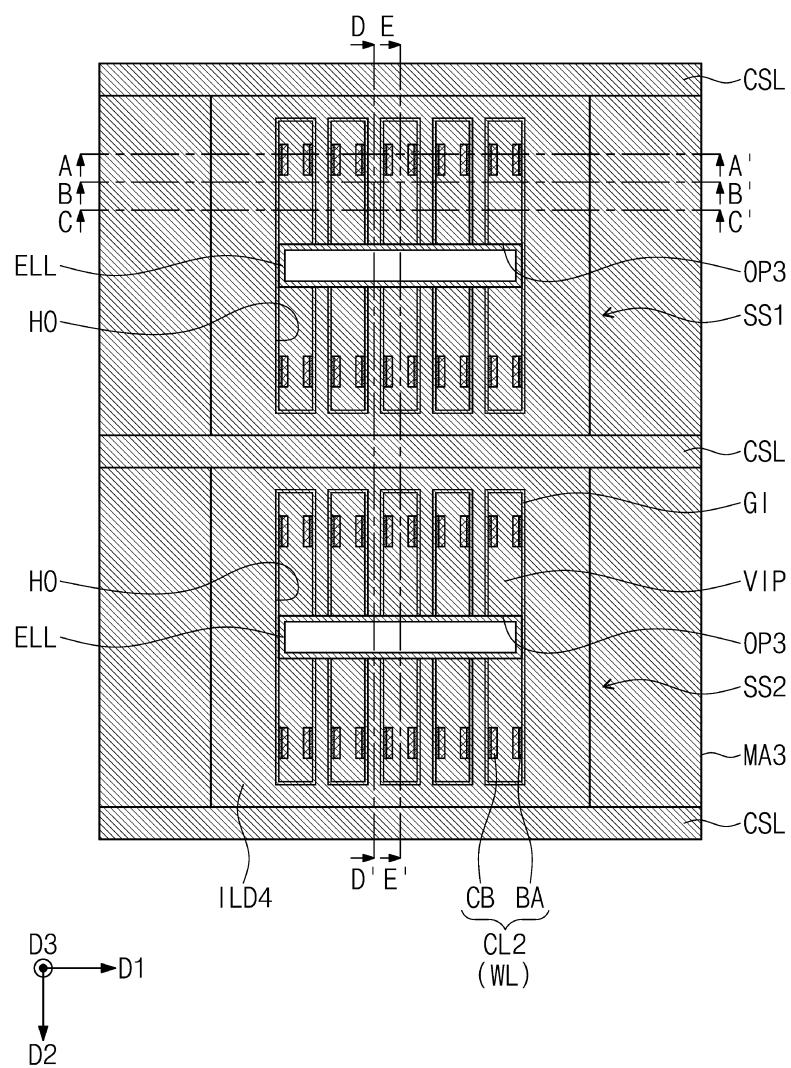


FIG. 33A

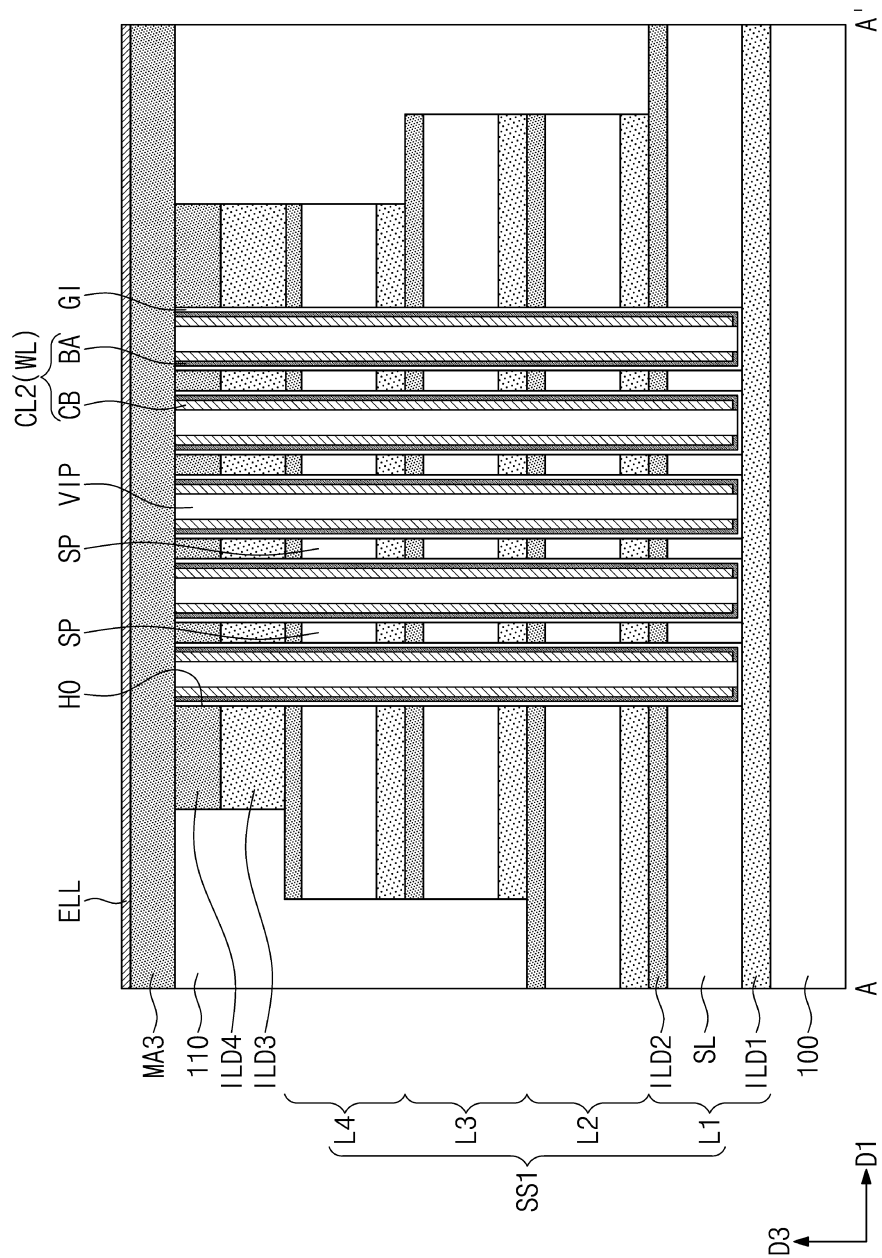


FIG. 33B

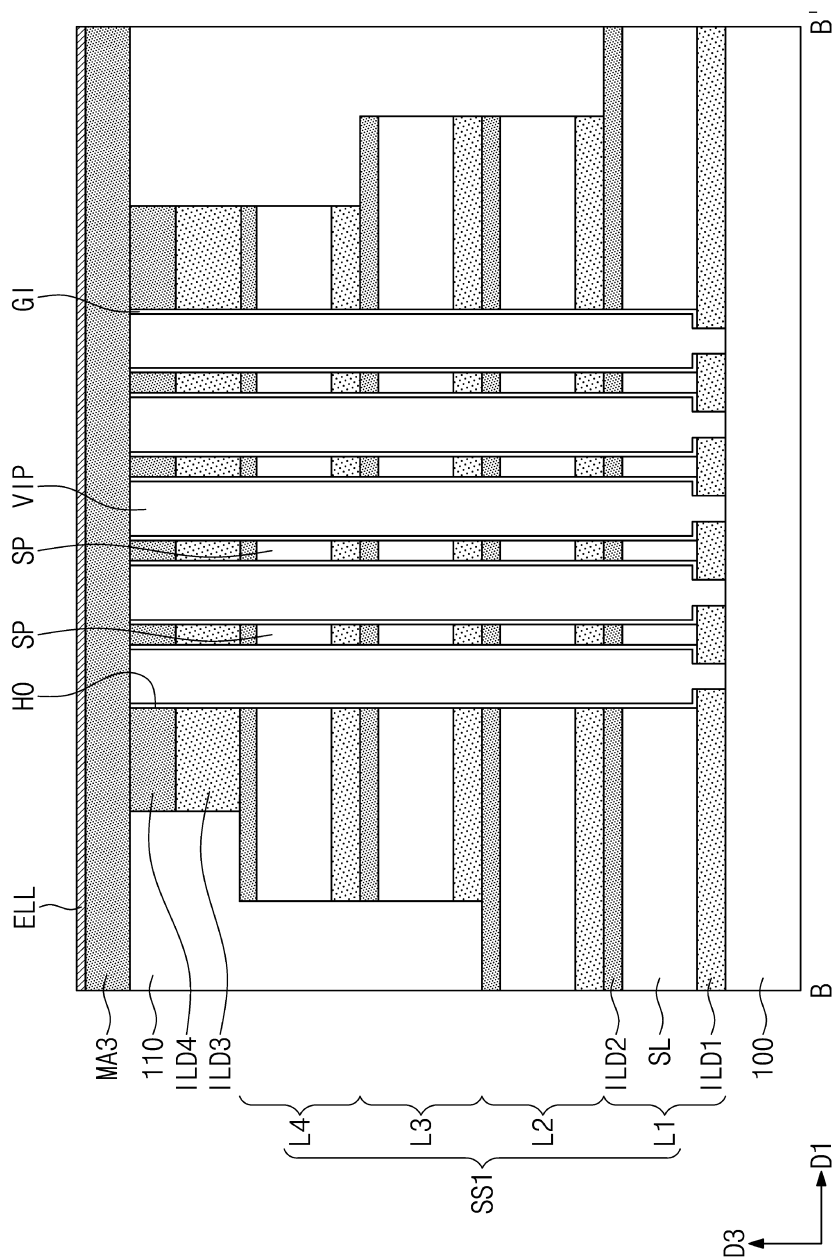
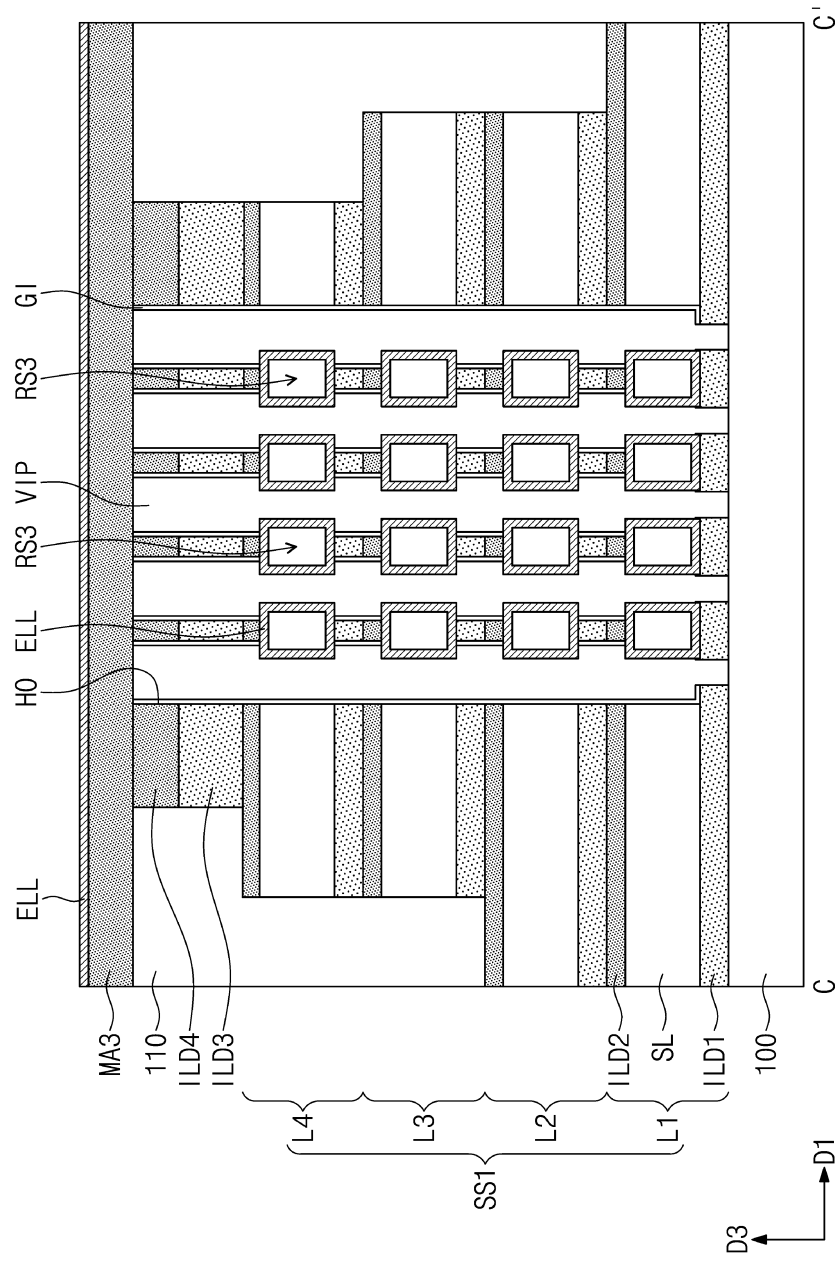


FIG. 33C



[illegible]

FIG. 33E

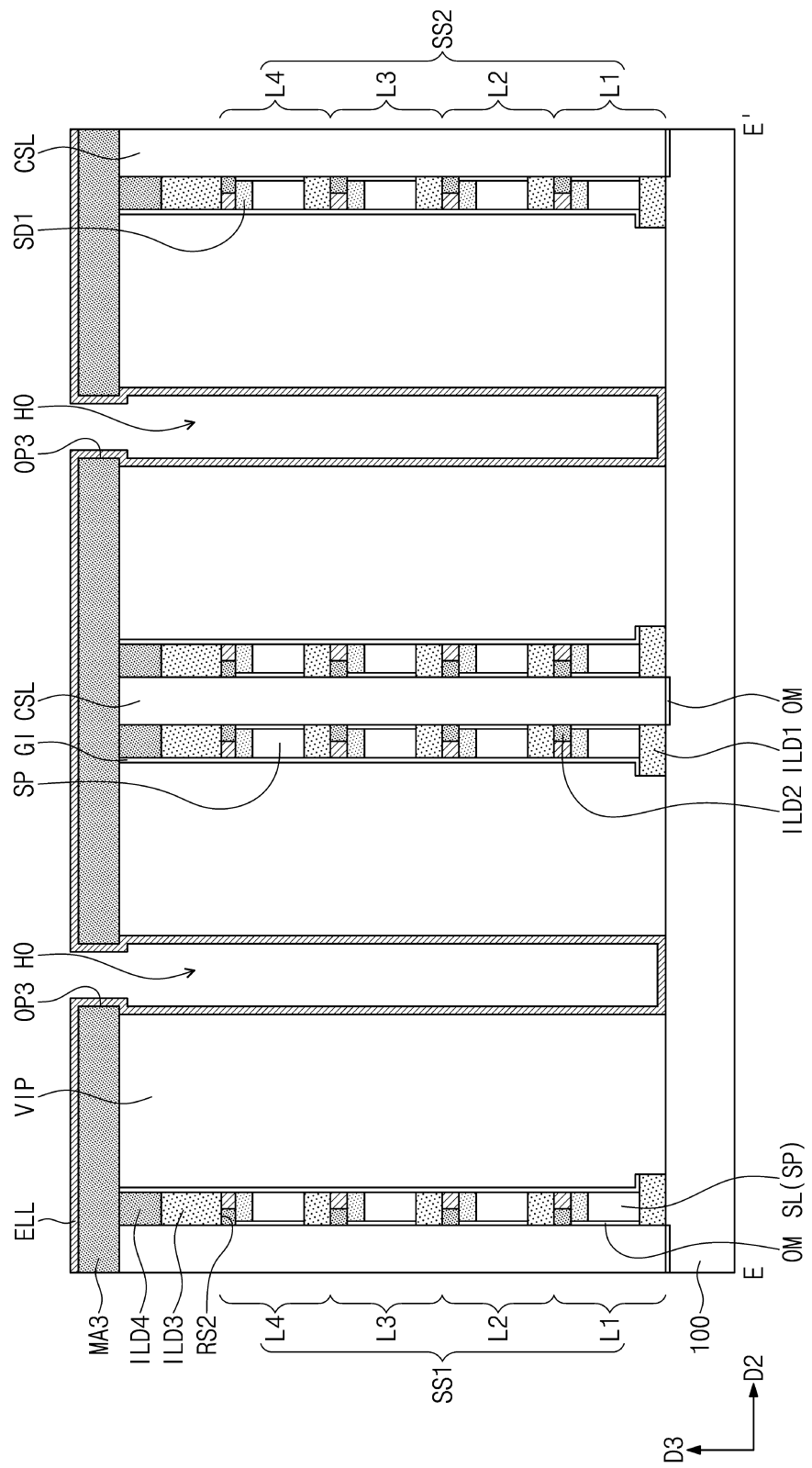


FIG. 34

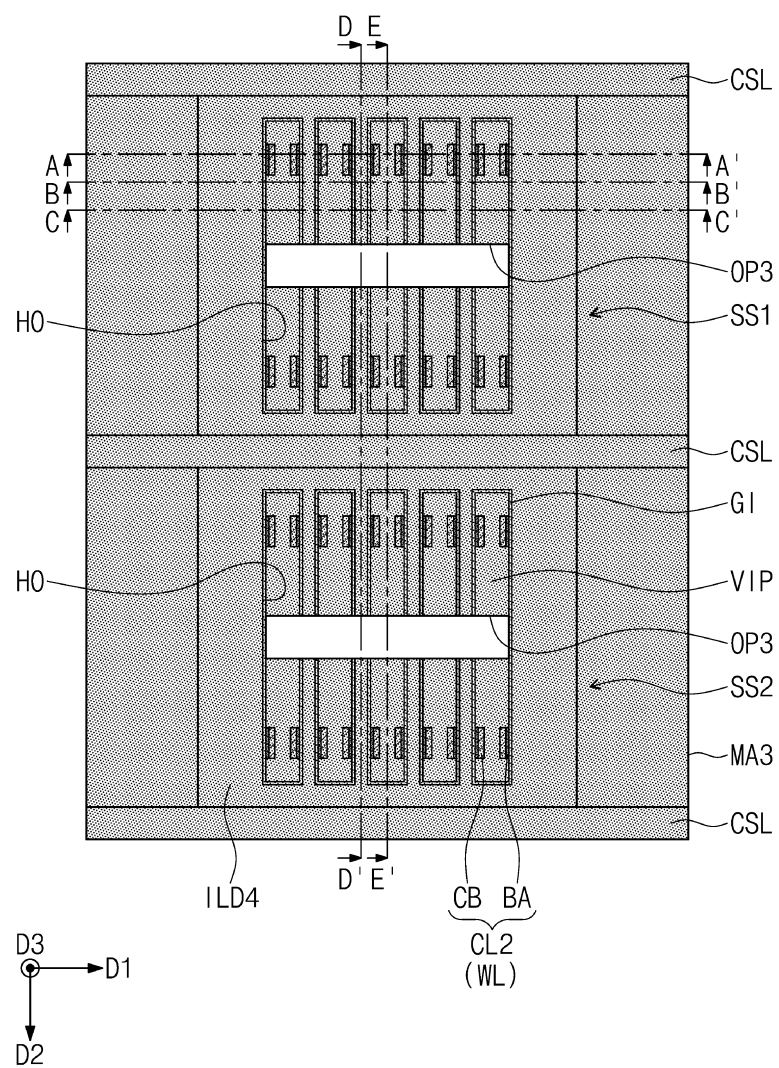


FIG. 35A

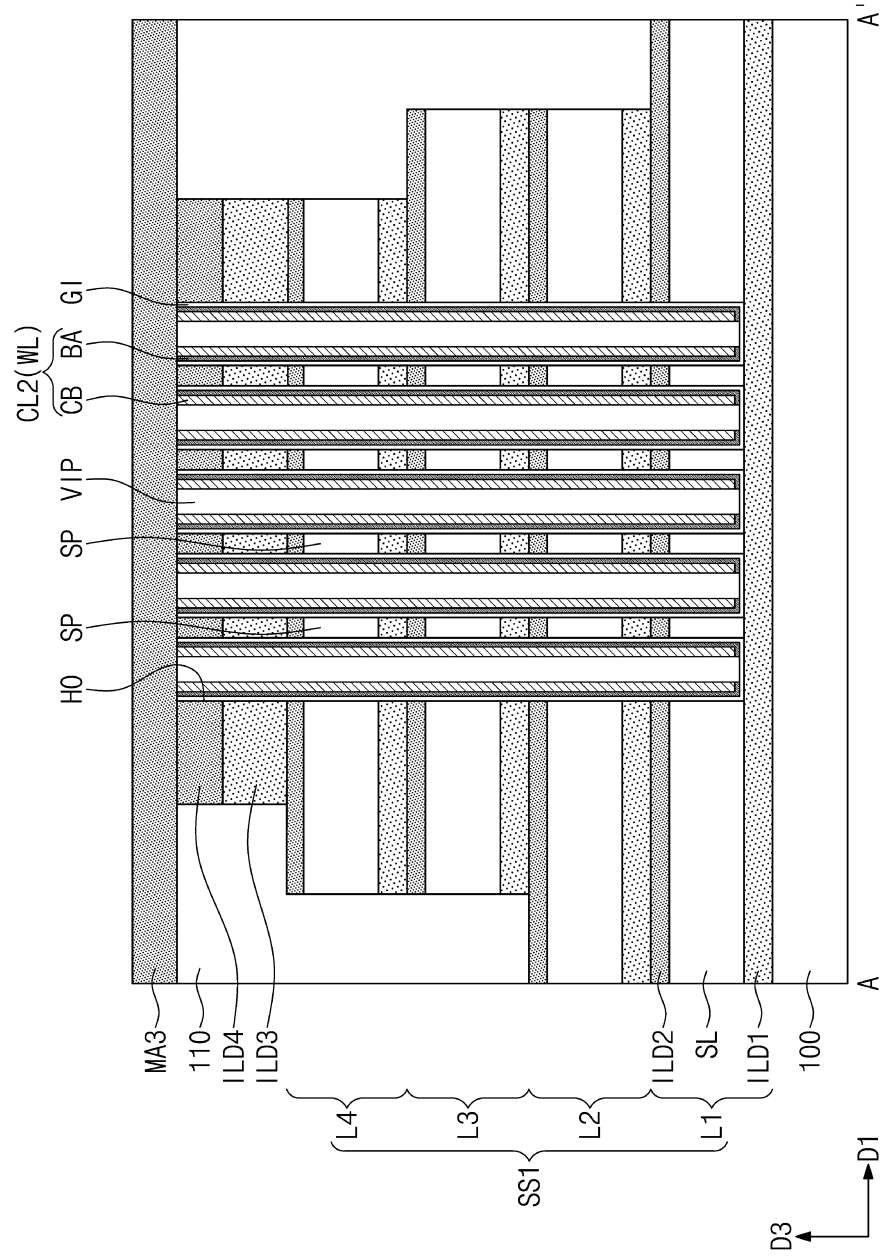


FIG. 31D

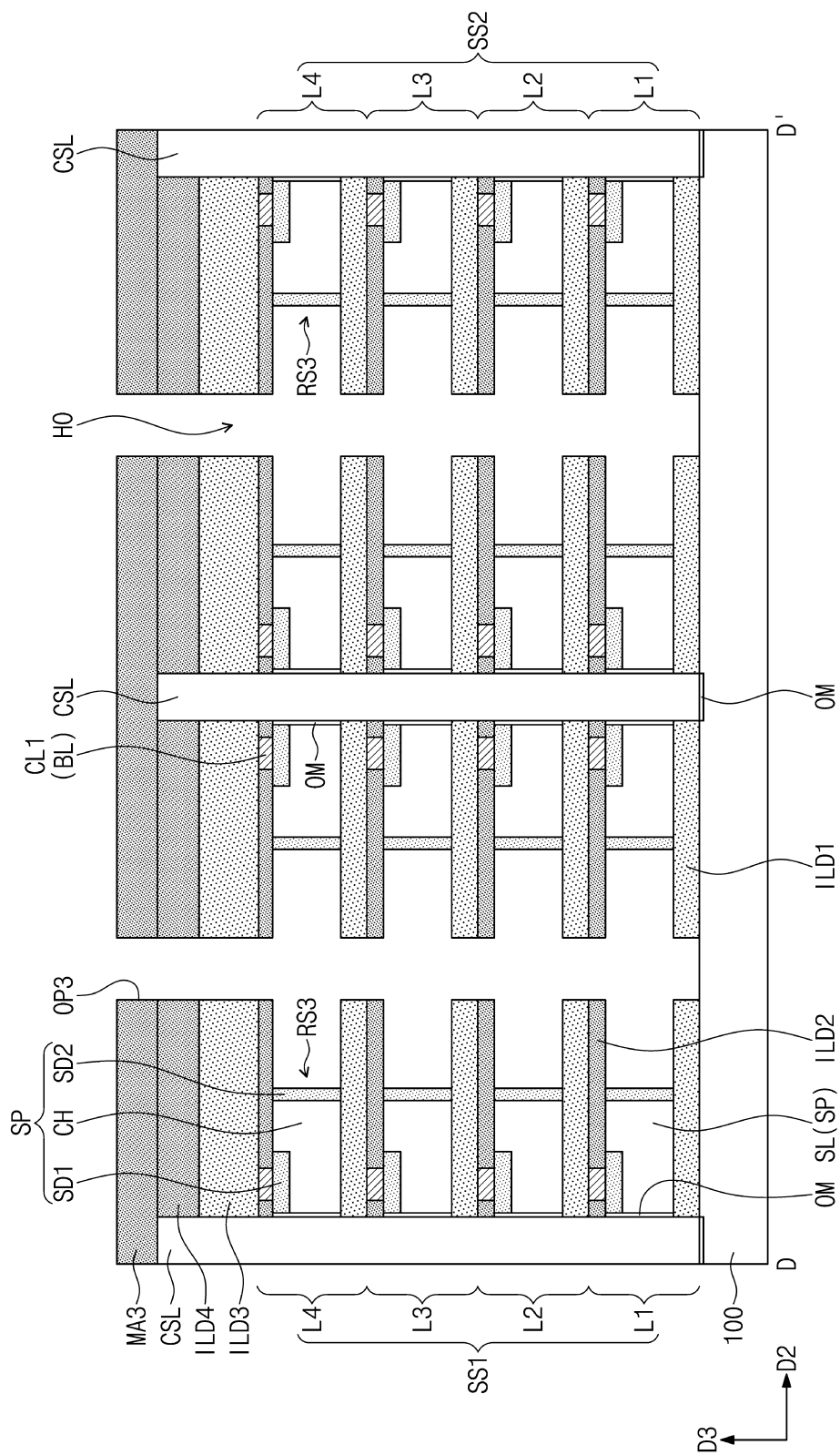


FIG. 35B

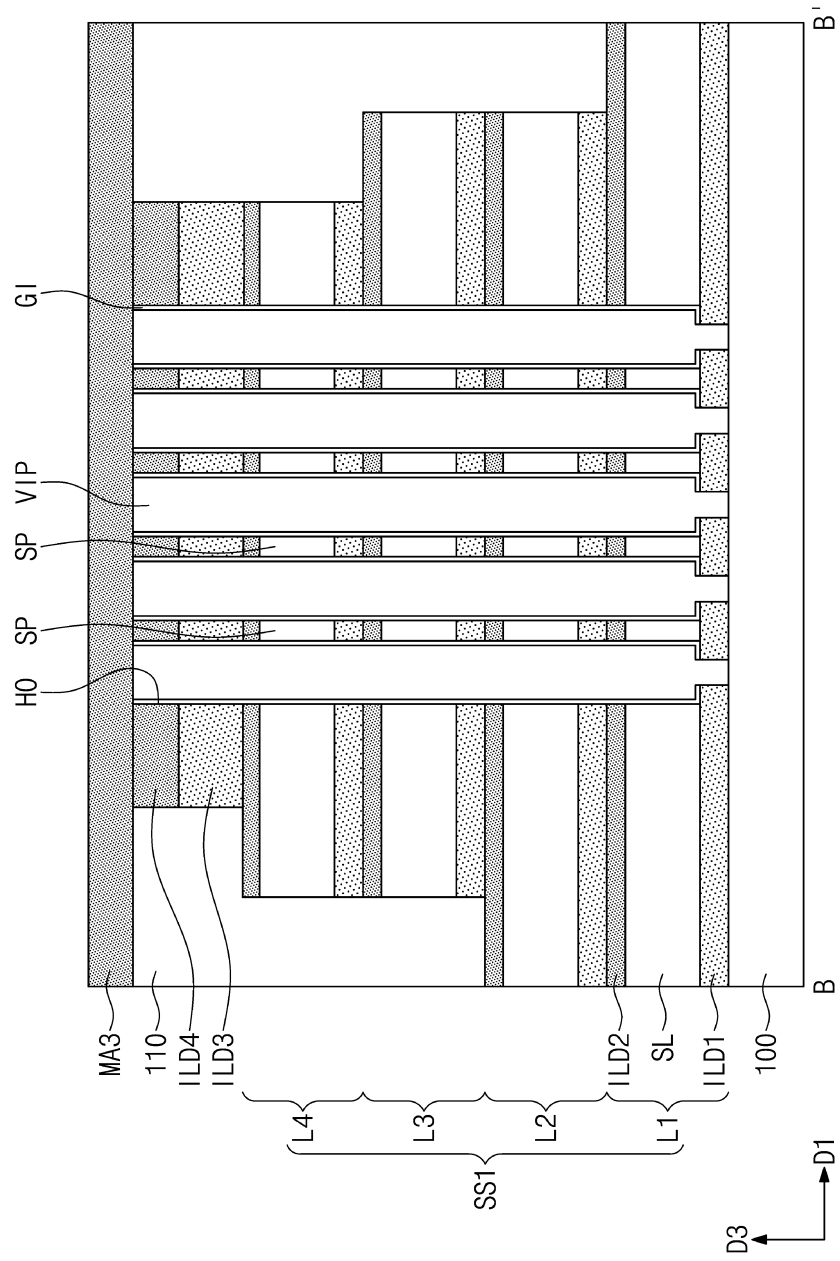


FIG. 35C

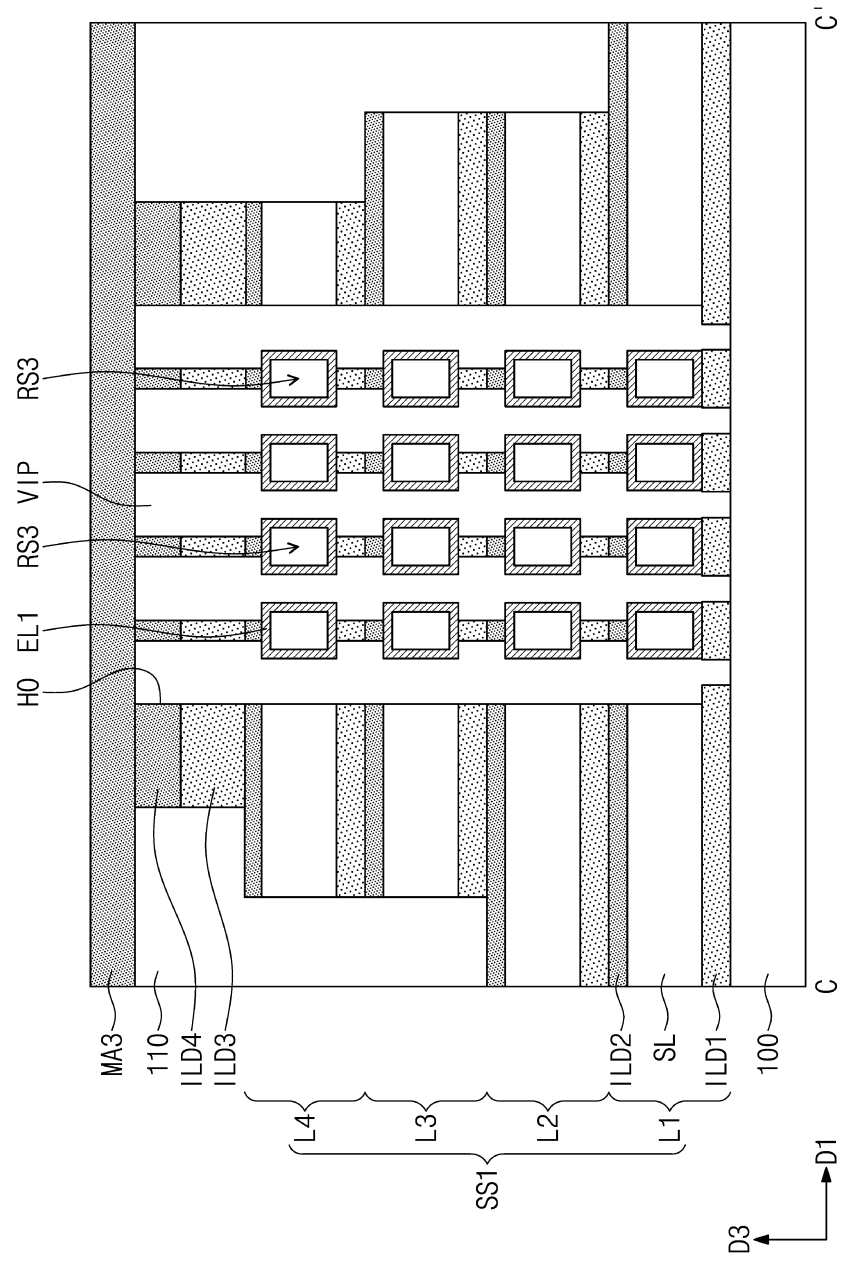


FIG. 35D

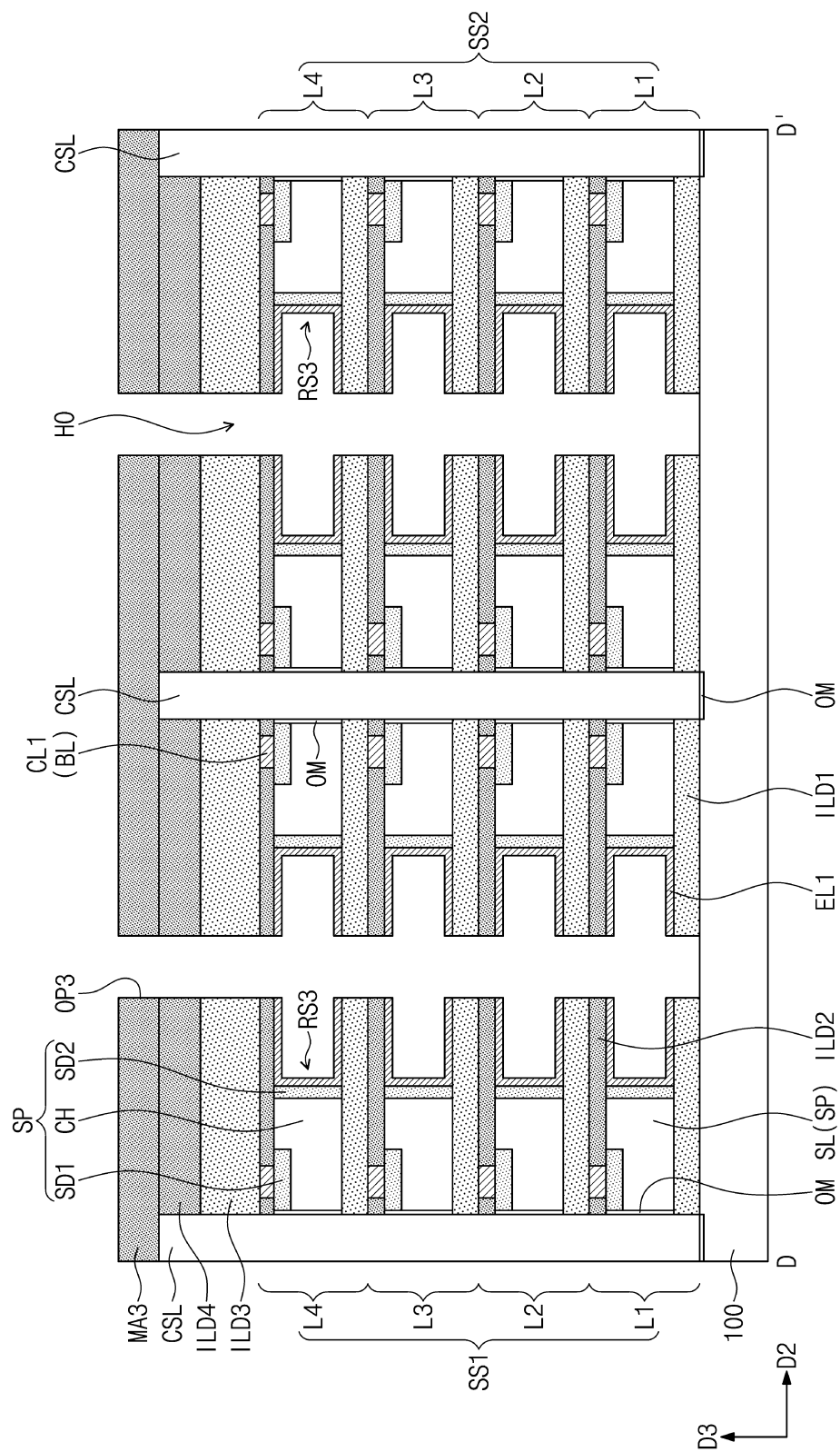


FIG. 35E

